

## Description

The SiT92216 is a 4 differential output and 1 LVCMOS output ultra low-jitter clock, fan-out buffer, intended to be used in low jitter, high frequency clock/data distribution. The low impedance LVCMOS outputs are designed to drive 50  $\Omega$  series or parallel terminated transmission lines.

The buffer can choose a clock input from primary, secondary or crystal source. The primary and secondary clock sources can be single ended or fully differential. The selected clock is distributed to 4 Differential and 1 LVCMOS output drivers.

The SiT92216 operates from a 3.3 V/2.5 V core supply and 3.3 V/2.5 V output supply. HCSL and LVCMOS output driver can be operated at 1.8 V. The core supply and output supply are independent of each other and no supply sequencing is required.

## Applications

- Carrier Ethernet
- 5G Wireless Basestations, 5G Small Cells

## Features

- Additive jitter performance of 50 fs RMS
- Typical output skew between clock outputs is 30 ps
- Support PCI-e Gen1 to Gen5
- Level translation with core supply voltage of 3.3 V/2.5 V and 3.3 V/2.5 V output supply for differential output drivers
- 1.8 V output supply support for LVCMOS and HCSL driver
- The device inputs consist of primary, secondary and crystal inputs
- The inputs are selected by programming input select pins of SiT92216. The input clock receiver in SiT92216 can accept LVPECL, LVDS, LVCMOS, SSTL, HCSL and OSC waveforms.
- Input frequencies are supported from DC to 2100 MHz are supported on primary and secondary inputs
- Crystal input can be over driven with frequency up to 250 MHz in crystal bypass mode
- SiT92216 buffer is available in a 32 pin, 5 mm x 5 mm QFN package

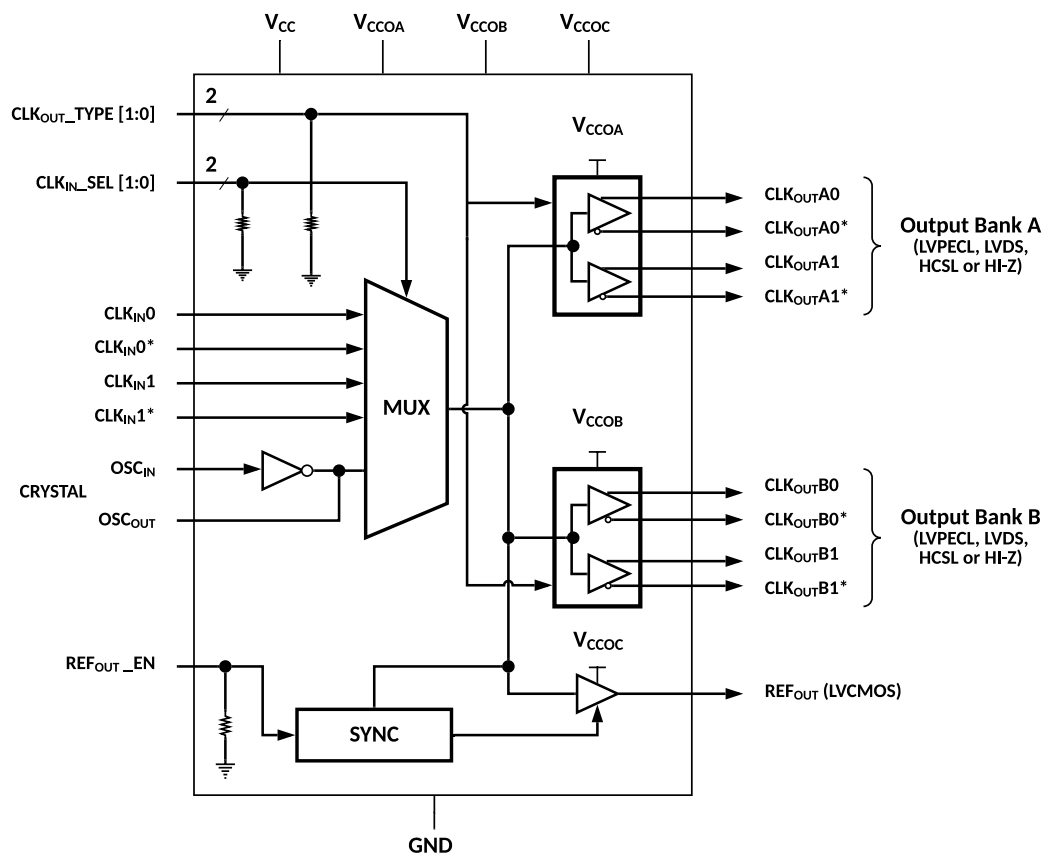


Figure 1. SiT92216 Block Diagram

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## Ordering Information

### SiT92216A I - P

**Part Family**

"SiT92216"

**Revision Letter**

"A" is the revision of Silicon

**Temperature Range**

"I": Industrial, -40°C to 85°C

**Packaging**

"P": 4Ku/reel option

## Electrical Characteristics

**Table 1. Absolute Maximum Ratings**

Parameters	Symbol	Min	Typ	Max	Units
Core supply voltage, Analog Input	$V_{CC}$	-0.3		3.6	V
Output bank supply voltage	$V_{CCO}$	-0.3		3.6	V
Input voltage, All Inputs, except $OSC_{IN}$	$V_{IN}$	-0.3		3.6	V
$OSC_{IN}$	$V_{IN}$	-0.3		1.5	V
Storage temperature	TS	-55		150	°C
Moisture Sensitivity Level	MSL	3			

**Notes:**

1. Exceeding maximum ratings may shorten the useful life of the device.
2. Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or at any other conditions beyond those indicated under the DC Electrical Characteristics is not implied. Exposure to Absolute-Maximum-Rated conditions for extended periods may affect device reliability or cause permanent device damage.

**Table 2. Recommended Operating Conditions**

Parameters	Symbol	Min	Typ	Max	Units
Core supply voltage	$V_{CC}$	3.135	3.3	3.45	V
	$V_{CC}$	2.375	2.5	2.625	V
Output supply voltage	$V_{CCOA/B}$	3.135	3.3	3.45	V
	$V_{CCOA/B}$	2.375	2.5	2.625	V
	$V_{CCOA/B}$ (Only for HCSSL)	1.71	1.8	1.89	V
Output supply voltage for LVCMOS driver	$V_{CCOC}$	3.135	3.3	3.45	V
	$V_{CCOC}$	2.375	2.5	2.625	V
	$V_{CCOC}$	1.71	1.8	1.89	V
Ambient Temperature	$T_A$	-40		85	°C
Junction Temperature	$T_J$			125	°C

**Table 3. Electrical Characteristics**

Unless otherwise specified:  $V_{CC} = 3.3\text{ V} \pm 5\%$ ,  $2.5\text{ V} \pm 5\%$ ,  $V_{CCO} = 3.3\text{ V} \pm 5\%$ ,  $2.5\text{ V} \pm 5\%$ ,  $-40\text{ }^{\circ}\text{C} \leq T_A \leq 85\text{ }^{\circ}\text{C}$ , CLKIn0/1 driven differentially, input slew rate  $\geq 3\text{ V/ns}$ . Typical values represent most likely parametric norms at  $V_{CC} = 3.3\text{ V}$ ,  $V_{CCO} = 3.3\text{ V}$ ,  $T_A = 25\text{ }^{\circ}\text{C}$ .

Parameter	Conditions	Symbol	Min	Typ	Max	Units
Core Supply Current, All Outputs Disabled	CLKIN0/1 selected	$I_{CC\_CORE}$		16.5	19.8	mA
	XO selected	$I_{CORE\_XO}^{(3)}$		11.4	14	
Frequency dependent current both bank on core supply. This current scales with frequency	For $F_{IN} = 2100\text{ MHz}$	$I_{CC\_DYN}^{(1)(3)}$		25	33	mA
Increment in core supply when all ODR banks are enabled		$I_{CC\_ODR\_EN}$			2	mA
Additive Output Supply Current, LVPECL Banks Enabled		$I_{CCO\_PECL}$		82	97.2	mA
Additive Output Supply Current, LVDS Banks Enabled		$I_{CCO\_LVDS}$		40	49	mA
Additive Output Supply Current, HCSL Banks Enabled		$I_{CCO\_HCSL}$		59	70.8	mA
Additive Output Supply Current, LVCMOS outputs Enabled	$F_{IN} = 200\text{ MHz}$ , $C_{LOAD} = 5\text{ pF}$ , $V_{CCO} = 3.3\text{ V}$	$I_{CCO\_CMOS}$		6	7.2	mA
	$F_{IN} = 200\text{ MHz}$ , $C_{LOAD} = 5\text{ pF}$ , $V_{CCO} = 2.5\text{ V}$			4.5	5.5	

**Notes:**

- Total current from core supply at frequency  $F_{IN} = I_{CORE\_STATIC} + N \cdot (0.5 \cdot I_{CC\_ODR\_EN}) + N \cdot (0.5 \cdot F_{IN} / 2100\text{M}) \cdot I_{CORE\_DYN}$ . Detailed methodology of calculating the power dissipated in each ODR mode is given in the section "Current consumption and Power Dissipation Calculations." N is the number of output banks enabled.
- Refer to [Application Information](#) Section for more information on current consumption and power dissipation calculations.
- Specification is ensured by characterization and is not tested in production.

**Table 4. Power Supply Ripple Rejection (PSRR)**

Parameter	Conditions	Symbol	Min	Typ	Max	Units
Ripple-Induced Phase Spur Level Differential LVPECL Output	$F_{IN} = 156.25\text{ MHz}$ , $V_{CCO} = 2.5\text{ V}$ , 100 KHz offset, 100m Vpp	$PSRR_{LVPECL}$		-67		dBc
Ripple-Induced Phase Spur Level Differential LVDS Output		$PSRR_{LVDS}$		-70		
Ripple-Induced Phase Spur Level Differential HCSL Output		$PSRR_{HCSL}$		-67.7		

**Notes:**

- Power supply ripple rejection, or PSRR, is defined as the single-sideband phase spur level (in dBc) modulated onto the clock output when a single-tone sinusoidal signal (ripple) is injected onto the  $V_{CCO}$  supply. Assuming no amplitude modulation effects and small index modulation, the peak-to-peak deterministic jitter (DJ) can be calculated using the measured single-sideband phase spur level (PSRR) as follows:  $DJ\text{ (ps pk-pk)} = [(2 \cdot 10^{(PSRR / 20)}) / (\pi \cdot f_{CLK})] \cdot 1\text{E}^{12}$
- Specification is ensured by characterization and is not tested in production.

**Table 5. Input Control Pin Characteristic**

Parameter	Conditions	Symbols	Min	Typ	Max	Units
Input Low Current		$I_{IL}$	-20	0.1		$\mu\text{A}$
Input high voltage – Logic inputs		$V_{IH}$	$0.7 \cdot V_{CC}$		$V_{CC}$	V
Input low voltage – Logic inputs		$V_{IL}$	GND		$0.3 \cdot V_{CC}$	V
Internal Pull-down resistance		$R_{pulldown}$		200		K $\Omega$

**Table 6. CMOS Control Inputs (CLKIN\_SELN, CLKOUT\_TYPEN, REFOUT\_EN)**

Parameter	Conditions	Symbol	Min	Typ	Max	Units
Low Level Input Voltage		$V_{IL}$	GND		$0.3 \cdot V_{CC}$	V
High Level Input Voltage		$V_{IH}$	$0.7 \cdot V_{CC}$		$V_{CC}$	
High Level Input Current	$V_{IH} = V_{CC} = 3.3 \text{ V}$	$I_{IH}$		30	50	uA
Low Level Input Current		$I_{IL}$	-20	0.1		

**Table 7. CLOCK INPUTS (CLKin0/CLKin0\*, CLKin1/CLKin1\*)**

Unless otherwise specified:  $V_{CC} = 3.3 \text{ V} \pm 5\%$ ,  $2.5 \text{ V} \pm 5\%$ ,  $V_{CCO} = 3.3 \text{ V} \pm 5\%$ ,  $2.5 \text{ V} \pm 5\%$ ,  $-40^\circ\text{C} \leq T_A \leq 85^\circ\text{C}$ , CLKin0/1 driven differentially, input slew rate  $\geq 3 \text{ V/ns}$ . Typical values represent most likely parametric norms at  $V_{CC} = 3.3 \text{ V}$ ,  $V_{CCO} = 3.3 \text{ V}$ ,  $T_A = 25^\circ\text{C}$ .

Parameter	Conditions	Symbol	Min	Typ	Max	Units
Input frequency range <sup>(4)</sup>		$F_{CLKin}$	DC		2100	MHz
Differential input high voltage	CLKin driven differentially	$V_{IHD}$			$V_{CC}$	V
Differential input low voltage		$V_{ILD}$	GND			V
Peak differential input voltage swing <sup>(2)</sup>		$V_{ID}$	0.15		1.3	V
Differential Input Common Mode Voltage	Input differential swing of 150 mV	$V_{CMD}$	0.25		$V_{CC}-1.2$	V
	Input differential swing of 350 mV		0.25		$V_{CC}-1.1$	V
	Input differential swing of 800 mV		0.25		$V_{CC}-0.9$	V
Single-Ended Input High Voltage	Inverting differential input held at $V_{CC}/2$ , $V_{CC} = 3.3 \text{ V}$	$V_{IH}$	2		$V_{CC}$	V
	Inverting differential input held at $V_{CC}/2$ , $V_{CC} = 2.5 \text{ V}$		1.6		$V_{CC}$	
Single-Ended Input Low Voltage	Inverting differential input held at $V_{CC}/2$ , $V_{CC} = 3.3 \text{ V}$	$V_{IL}$	GND		1.3	V
	Inverting differential input held at $V_{CC}/2$ , $V_{CC} = 2.5 \text{ V}$		GND		0.9	
Single ended input voltage swing <sup>(3)</sup>		$V_{LSE}$	0.3		2	Vpp
Single-Ended Input Common Mode Voltage		$V_{CM}$	0.25		$V_{CC}-1.2$	V
Mux Isolation, CLKin0 to CLKin1	$F_{in} = 100 \text{ MHz}$ , Foffset > 50 KHz	$ISO_{MUX}^{(1)}$		-84		dBc
	$F_{in} = 200 \text{ MHz}$ , Foffset > 50 KHz			-82		
	$F_{in} = 500 \text{ MHz}$ , Foffset > 50 KHz			-71		
	$F_{in} = 1000 \text{ MHz}$ , Foffset > 50 KHz			-65		

**Table 8. Crystal Interface (OSC<sub>IN</sub>, OSC<sub>OUT</sub>)**

Parameter	Conditions	Symbol	Min	Typ	Max	Units
Equivalent series resistance		ESR		35	60	Ω
Load capacitance		CL	6	8	10	pF
Shunt Capacitance		Co		2	3	pF
Power dissipated in the crystal		Drive level		100	200	uW
Mode of oscillation				Fundamental		
Crystal frequency range		F <sub>OSC</sub> <sup>(1)</sup>	8		50	MHz
External clock frequency range	XO over drive or Bypass mode	F <sub>CLK</sub>			250	MHz
Maximum swing level on OSC <sub>in</sub> /OSC <sub>out</sub> pins	XO over drive or Bypass mode	V <sub>max</sub>			1.5	V
Additive jitter <sup>(3)</sup>	RMS, integration BW 12 KHz to 5 MHz, F <sub>crystal</sub> = 25 MHz. Crystal input select Measured at V <sub>CC</sub> = V <sub>CCO</sub> = 2.5 V	t <sub>jit</sub> <sup>(1)</sup>		155		fs(rms)
External clock frequency range	XO over drive or Bypass mode	F <sub>CLK</sub>			250	MHz

**Notes:**

1. Specification is ensured by characterization and is not tested in production.
2. Refer to [Parameter Measurement Information](#) for definition of VID and VOD voltages.
3. For clock input frequency ≥ 100 MHz, CLK<sub>in</sub>X can be driven with single-ended (LVCMOS) input swing up to 3.3 Vpp. For clock input frequency < 100 MHz, the single-ended input swing should be limited to 2 Vpp max to prevent input saturation (refer to Driving the Clock Inputs for interfacing 2.5 V/3.3 V LVCMOS clock input < 100 MHz to CLK<sub>in</sub>X).
4. If the input clock is initially absent when the chip is just powered up, it will take atleast 2 falling edge of clock cycles for the output to appear. Therefore, the buffer level translates DC only after it sees two consecutive falling edge of input clock

**Table 9. LVPECL OUTPUTS (CLK<sub>OUTAn</sub>/CLK<sub>OUTAn</sub>\*, CLK<sub>OUTBn</sub>/CLK<sub>OUTBn</sub>\*)**

Unless otherwise specified:  $V_{CC} = 3.3 \text{ V} \pm 5\%$ ,  $2.5 \text{ V} \pm 5\%$ ,  $V_{CCO} = 3.3 \text{ V} \pm 5\%$ ,  $2.5 \text{ V} \pm 5\%$ ,  $-40^\circ\text{C} \leq T_A \leq 85^\circ\text{C}$ , CLK<sub>in</sub>0/1 driven differentially, input slew rate  $\geq 3 \text{ V/ns}$ . Typical values represent most likely parametric norms at  $V_{CC} = 3.3 \text{ V}$ ,  $V_{CCO} = 3.3 \text{ V}$ ,  $T_A = 25^\circ\text{C}$ . Termination is  $50 \Omega$  to  $V_{CCO} - 2\text{V}$

Parameter	Conditions	Symbol	Min	Typ	Max	Units
<b>Maximum Output Frequency Full VOD Swing</b>	Maximum output frequency, full VOD swing $\geq 600 \text{ mV}$ $50 \Omega$ termination biased with $V_{CCO} - 2\text{V}$	F <sub>CLKOUT_FS</sub>	1000	1200		MHz
<b>Maximum Output Frequency Reduced VOD Swing</b>	Maximum output frequency, full VOD swing $\geq 400 \text{ mV}$ $50 \Omega$ termination biased with $V_{CCO} - 2\text{V}$		1500	2100		MHz
<b>Additive RMS Jitter, Integration Bandwidth 12 kHz to 20 MHz</b>	Integration bandwidth from 12 kHz to 20 MHz, FIN = 156.25 MHz, SR > 3 V/ns $50 \Omega$ termination biased with $V_{CCO} - 2\text{V}$ , FIN = 156.25 MHz, SR > 3 V/ns	JitterADD		55	88	fs(rms)
<b>Noise Floor f<sub>OFFSET</sub> <math>\geq 10 \text{ MHz}</math></b>	$50 \Omega$ termination biased with $V_{CCO} - 2\text{V}$ , FIN = 156.25 MHz, SR > 3 V/ns	Noise <sub>FLOOR</sub>		-159		dBc/Hz
<b>Duty Cycle</b>	$50 \Omega$ termination biased with $V_{CCO} - 2\text{V}$	ODC	45		55	%
<b>Output High Voltage</b>	$50 \Omega$ termination biased with $V_{CCO} - 2\text{V}$	V <sub>OH</sub>	$V_{CCO} - 1.165$		$V_{CCO} - 0.75$	V
<b>Output Low Voltage</b>	$50 \Omega$ termination biased with $V_{CCO} - 2\text{V}$	V <sub>OL</sub>	$V_{CCO} - 2.0$		$V_{CCO} - 1.45$	V
<b>Output Voltage Swing</b>	$50 \Omega$ termination biased with $V_{CCO} - 2\text{V}$	V <sub>OD</sub>	0.5		0.86	V
<b>Output Rise Time 20% to 80%</b>	$50 \Omega$ termination biased with $V_{CCO} - 2\text{V}$	t <sub>R</sub>		210	350	ps
<b>Output Fall Time 80% to 20%</b>	$50 \Omega$ termination biased with $V_{CCO} - 2\text{V}$	t <sub>F</sub>		210	350	ps

**Table 10. LVDS Outputs (CLK<sub>OUTAn</sub>/CLK<sub>OUTAn</sub>\*, CLK<sub>OUTBn</sub>/CLK<sub>OUTBn</sub>\*)**

Parameter	Conditions	Symbol	Min	Typ	Max	Units
Maximum Output Frequency Full VOD Swing	R <sub>L</sub> = 100 Ω, differential	F <sub>CLKOUT_FS</sub>	1000	1600	-	MHz
Maximum Output Frequency Reduced VOD Swing	R <sub>L</sub> = 100 Ω, differential		1500	2100		MHz
Additive RMS Jitter, Integration Bandwidth 12 kHz to 20 MHz	Integration bandwidth from 12 KHz to 20 MHz, F <sub>in</sub> = 156.25 MHz, SR > 3 V/ns R <sub>L</sub> = 100 Ω, differential	Jitter <sub>ADD</sub>		60	82	fs(rms)
Noise Floor f <sub>OFFSET</sub> ≥ 10 MHz	F <sub>in</sub> = 156.25 MHz, SR > 3 V/ns R <sub>L</sub> = 100 Ω, differential	Noise <sub>FLOOR</sub>		-159		dBc
Duty Cycle	R <sub>L</sub> = 100 Ω, differential	ODC	45		55	%
Output Voltage Swing			247		454	mV
Change in Magnitude of VOD for Complementary Output States	R <sub>L</sub> = 100 Ω, differential	ΔV <sub>PP</sub>			50	mV
Output Offset Voltage	LVDS common mode	V <sub>OS</sub>	1.125	1.25	1.375	V
Change in Magnitude of VOS for Complementary Output States		Δ V <sub>OS</sub>			50	mV
Output Short Circuit Current Single Ended					9.6	mA
Output Short Circuit Current Differential					9.6	mA
Output Rise Time 20% to 80%	R <sub>L</sub> = 100 Ω, differential, CL < 5 pF	t <sub>R</sub>		210	350	ps
Output Fall Time 80% to 20%	Uniform transmission line up to 10 inches with characteristic impedance of 50 Ω	t <sub>F</sub>		210	350	ps

Table 11. LVCMOS Output (REF<sub>OUT</sub>)

Parameter	Conditions		Symbol	Min	Typ	Max	Units
Output Frequency Range			f <sub>CLKOUT</sub>	0		250	MHz
Additive RMS Jitter Integration Bandwidth 12KHz to 20 MHz	V <sub>CCOC</sub> = 3.3 V ± 5%		Jitter <sub>ADD</sub>		22	45	fs(rms)
	V <sub>CCOC</sub> = 2.5 V ± 5%				24	43	
Noise Floor f <sub>OFFSET</sub> ≥ 10 MHz	V <sub>CCOC</sub> = 3.3 V ± 5%		Noise <sub>FLOOR</sub>		-159		dBc
	V <sub>CCOC</sub> = 2.5 V ± 5%				-157		
Duty Cycle	Fin<=200Mhz		ODC	45		55	%
	Fin>200Mhz			40		60	%
Output High Voltage	V <sub>CCOC</sub> = 3.3 V ± 5%, 1 mA pull down current V <sub>CCOC</sub> = 2.5 V ± 5%, 1 mA pull down current		V <sub>OH</sub>	V <sub>CCOC</sub> -0.1 V			V
Output Low Voltage	V <sub>CCOC</sub> = 3.3 V ± 5%, 1 mA pull down current V <sub>CCOC</sub> = 2.5 V ± 5%, 1 mA pull down current		V <sub>OL</sub>			0.1	V
Output High Current(Source)	V <sub>O</sub> =V <sub>CCO</sub> /2	V <sub>CCO</sub> = 3.3 V			79		mA
		V <sub>CCO</sub> = 2.5 V			51		
Output Low Current(Sink)	V <sub>O</sub> =V <sub>CCO</sub> /2	V <sub>CCO</sub> = 3.3 V			70		
		V <sub>CCO</sub> = 2.5 V			46		
Output Rise Time20% to 80%	C <sub>LOAD</sub> = 5 pF, R <sub>LOAD</sub> = 50 Ω AC coupled		t <sub>R</sub>		250	450	ps
Output Fall Time 80% to 20%	C <sub>LOAD</sub> = 5 pF, R <sub>LOAD</sub> = 50 Ω AC coupled		t <sub>F</sub>		250	450	ps
Output Enable Time			t <sub>EN</sub> <sup>(1)</sup>			4	cycles
Output Disable Time			t <sub>DIS</sub> <sup>(1)</sup>			4	cycles

Table 12. Propagation Delay and Output Skew

Parameter	Conditions	Symbol	Min	Typ	Max	Units
Propagation Delay CLKin-to-LVPECL	50 Ω termination biased with V <sub>CCO</sub> - 2V	tpd	723	818	931	ps
Propagation Delay CLKin-to-LVDS		tpd	726	826	944	ps
Propagation Delay CLKin-to-HCSL		tpd	705	820	897	ps
Propagation Delay CLKin-to-LVCMOS	V <sub>CCO</sub> = 3.3 V, PCB trace of 5 inch, 5 pF capacitor	td <sup>(1)</sup>		1.4	2.5	ns
	V <sub>CCO</sub> = 2.5 V, PCB trace of 5 inch, 5 pF capacitor			1.5	2.7	ns
Output Skew LVPECL/LVDS/HCSL	V <sub>CCO</sub> = 3.3 V, 2.5 V	Tsk(o) <sup>1</sup>			31	ps
Part-to-Part Output Skew LVPECL/LVDS/HCSL		Tsk(p-p) <sup>1</sup>			50	ps

## Notes:

1. Specification is ensured by characterization and is not tested in production.

**Table 13. HCSL Outputs (CLK<sub>OUTAn</sub>/CLK<sub>OUTAn</sub>\*, CLK<sub>OUTBn</sub>/CLK<sub>OUTBn</sub>\*)**

Parameters	Conditions	Symbol	Min	Typ	Max	Units
Output Frequency Range	R <sub>L</sub> = 50 Ω to GND	F <sub>CLKOUT_FS</sub>	DC		700	MHz
Additive RMS Jitter Integration Bandwidth 12kHz to 20 MHz	Integration bandwidth from 12 KHz to 20 MHz, F <sub>IN</sub> = 156.25 MHz, SR > 3 V/ns R <sub>L</sub> = 50 Ω to GND	Jitter <sub>ADD</sub>		55	86	fs(rms)
Noise Floor f <sub>OFFSET</sub> ≥ 10 MHz		Noise <sub>FLOOR</sub>		-159		dBc
Duty Cycle		ODC	45		55	%
Output High Voltage		V <sub>OH</sub>	600	840	1150	mV
Output Low Voltage		V <sub>OL</sub>	-150	28	150	mV
Absolute Crossing Voltage	R <sub>L</sub> = 50 Ω to GND, C <sub>L</sub> < 5 pF	V <sub>CROSS</sub>	250		550	mV
Total Variation of V <sub>CROSS</sub>		V <sub>CROSSDELTA</sub>			140	mV
Output Rise Time 20% to 80%	F <sub>IN</sub> = 156.25 MHz, Uniform transmission line up to 10 inches with characteristic impedance of 50 Ω R <sub>L</sub> = 50 Ω to GND, C <sub>L</sub> < 5 pF	t <sub>R</sub>		210	500	ps
Output Fall Time 80% to 20%		t <sub>F</sub>		210	500	ps

**Table 14. ESD Ratings**

Parameter	Conditions	Symbol	Value	Units
Electrostatic Discharge	Human Body Model		±2000	V
	Charged Device Model		±1500	

**Table 15. Thermal Characteristics**

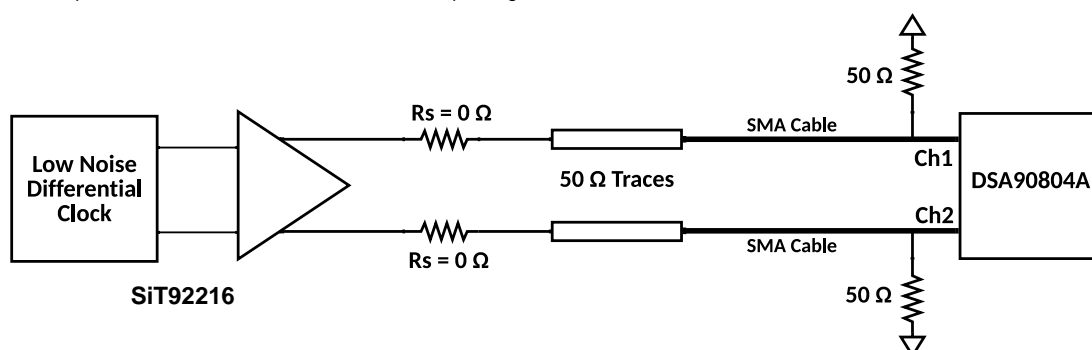
Parameter	Symbol	Min	Typ	Max	Units
Junction to ambient thermal resistance	θ <sub>JA</sub>		37.4		°C/W
Junction to board	θ <sub>JB</sub>		16.62		°C/W
Junction to case	θ <sub>JC</sub>		23.7		°C/W
Junction to top characterization parameter	ψ <sub>JT</sub>		0.75		°C/W

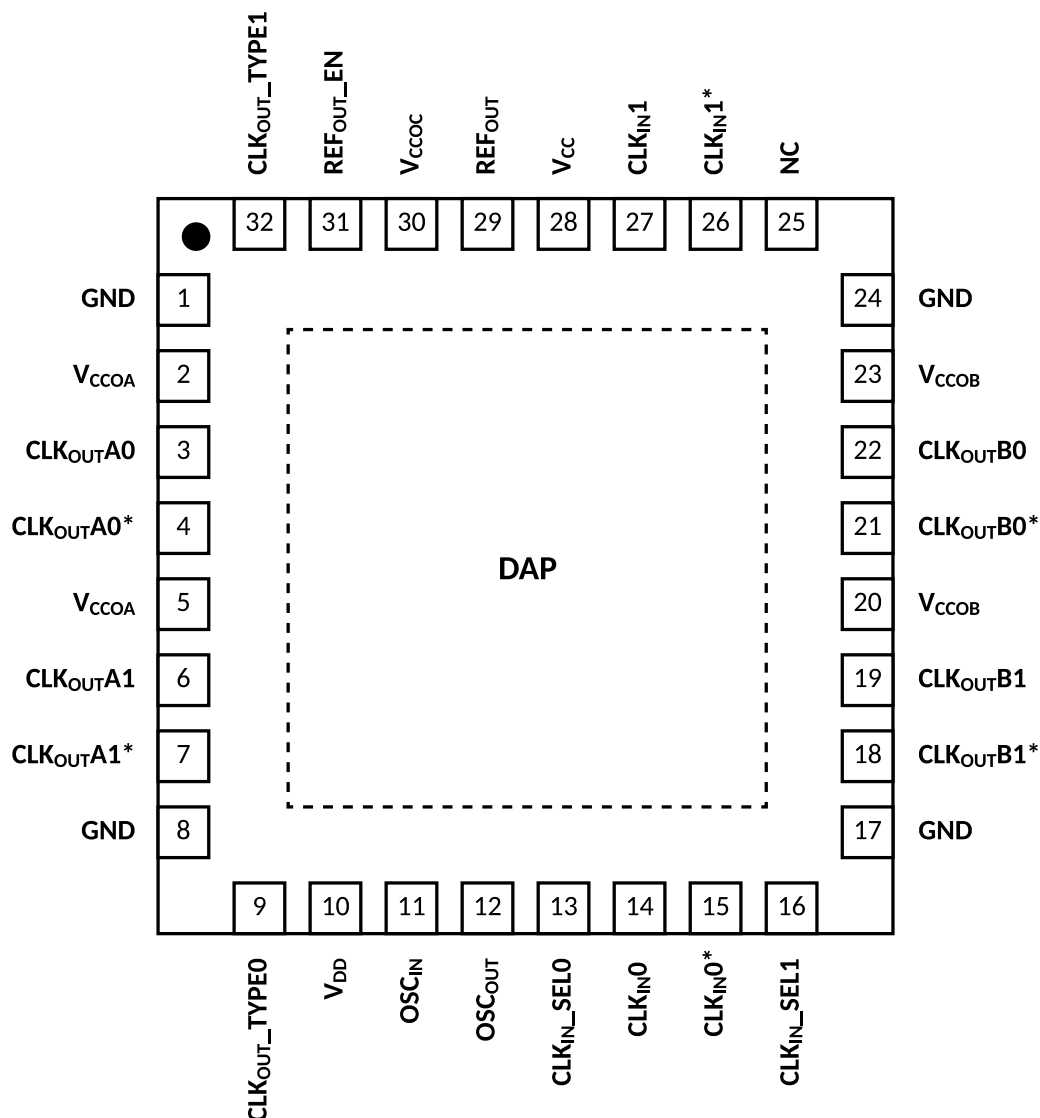
**Table 16. Filtered Phase Jitter Parameters - PCIe Common Clocked (CC) Architecture**

Parameters	Conditions	Symbol	Min	Typ	Max	Units
<b>Additive Phase Jitter</b>	PCIe Gen 1 <sup>[1-6]</sup>	$t_{jphPCIeG1-CC}$		2	5	ps (p-p)
	PCIe Gen 2 <sup>[1-6]</sup>	$t_{jphPCIeG2-CC}$		0.08	0.15	ps(rms)
	PCIe Gen 3 <sup>[1-6]</sup>	$t_{jphPCIeG3-CC}$		0.03	0.07	ps(rms)
	PCIe Gen4 <sup>[1-6]</sup>	$t_{jphPCIeG4-CC}$		0.03	0.07	ps(rms)
	PCIe Gen5 <sup>[1-6]</sup>	$t_{jphPCIeG5-CC}$		0.01	0.02	ps(rms)

**Notes:**

1. Applies to all the differential outputs, guaranteed by design and characterization.
2. Applies to all the Outputs when driven by a low phase noise source SMA100B.
3. Additive RMS Jitter Measurements were made using DSA90804A for minimum waveform length of  $\geq 100k$  cycles with a minimum sampling rate of  $\geq 40GSa/s$  with the waveform covering 90% of the DSO screen. All the post processing the DSO is disabled to decrease the additional jitter impact from oscilloscope. Broadband oscilloscope noise is also minimized in the measurement.
4. Additive jitter for RMS values is calculated by solving the equation for b [  $b = \sqrt{c^2 - a^2}$  ] where 'a' the rms input jitter and "c" is the rms total jitter.
5. Input to SiT92216 is fed using low phase noise source SMA100B, SiT92216 is configured as 100MHz HCSL Output Driver [VCCOx = 3.3V] and fed to the channels of DSA90804A using the exact measurement set up [Refer Note 6 ]
6. SiT92216 PCI Express Additive RMS Jitter Measurement Set up configuration



**Figure 2. SiT92216 Top View****Table 17. Detailed Pin Description**

Pin Name	I/O Type	Pin No	Function
DAP	GND	DAP	Die Attach Pad. Connect to the PCB ground plane for heat dissipation
GND	GND	1,8,17, 24	Ground
V <sub>CCOA</sub>	Power	2, 5	Power supply for Bank A Output buffers. V <sub>CCOA</sub> operates from 3.3 V or 2.5 V. 1.8 V is supported for HCSL driver. The V <sub>CCOA</sub> pins are internally tied together. Bypass with a 0.1 uF low-ESR capacitor placed very close to each V <sub>CCO</sub> pin. <sup>(2)</sup>
CLK <sub>OUT</sub> A0,	Output	3	Differential clock output A0. Output type set by CLK <sub>OUT</sub> _TYPE pins
CLK <sub>OUT</sub> A0*		4	
CLK <sub>OUT</sub> A1	Output	6,	Differential clock output A1. Output type set by CLK <sub>OUT</sub> _TYPE pins.
CLK <sub>OUT</sub> A1*		7	
CLK <sub>OUT</sub> TYPE0	Power	9	Bank A and Bank B output buffer type selection pins <sup>(3)</sup>
CLK <sub>OUT</sub> TYPE1		32	
V <sub>CC</sub>	Input	10, 28	Power supply for Core and Input Buffer blocks. The V <sub>CC</sub> supply operates from 3.3 V or 2.5 V. Bypass with a 0.1 uF low-ESR capacitor placed very close to each V <sub>CC</sub> pin.
OSC <sub>IN</sub>	Input	11	Input for crystal can also be driven by a XO, TCXO, or other external single-ended clock.

Pin Name	I/O Type	Pin No	Function
OSC <sub>OUT</sub>	Output	12	Output for crystal. Leave OSC <sub>OUT</sub> floating if OSC <sub>IN</sub> is driven by a single ended clock.
CLK <sub>IN</sub> SEL0	Input	13	Clock input selection pins <sup>(3)</sup>
CLK <sub>IN</sub> SEL1		16	
CLK <sub>IN</sub> 0	Input	14	Universal clock input 0 (differential/single-ended)
CLK <sub>IN</sub> 0*		15	
CLK <sub>OUT</sub> B1*	Output	18	Differential clock output B1. Output type set by CLK <sub>OUT</sub> _TYPE pins.
CLK <sub>OUT</sub> B1		19	
V <sub>CCOB</sub>	Power	20, 23	Power supply for Bank B Output buffers. V <sub>CCOB</sub> operates from 3.3 V or 2.5 V. 1.8 V is supported for HCSL driver. The V <sub>CCOB</sub> pins are internally tied together. Bypass with a 0.1 uF low-ESR capacitor placed very close to each V <sub>CCO</sub> pin. Refer <a href="#">Table 1</a>
CLK <sub>OUT</sub> B0*	Output	21	Differential clock output B0. Output type set by CLK <sub>OUT</sub> _TYPE pins.
CLK <sub>OUT</sub> B0		22	
NC		25	Not Connected
CLK <sub>IN</sub> 1*	Input	26	Universal clock input 1 (differential/single-ended)
CLK <sub>IN</sub> 1		27	
REF <sub>OUT</sub>	Output	29	LVCMOS reference output. Enable output by pulling REF <sub>OUT</sub> EN pin high.
V <sub>CCOC</sub>	Power	30	Power supply for REF <sub>OUT</sub> buffer. V <sub>CCOC</sub> operates from 3.3 V or 2.5 V or 1.8 V Bypass with a 0.1 uF low-ESR capacitor placed very close to each V <sub>CCO</sub> pin. <sup>(2)</sup>
REF <sub>OUT</sub> EN	Input	31	REF <sub>OUT</sub> enable input. Enable signal is internally synchronized to selected clock input <sup>(3)</sup>

## Functional Description

### Functional Block Diagram

The SiT92216 is a 4 differential output, 1 LVCMOS clock fan out buffer with low additive jitter that can operate up to 2.1 GHz. It features a 3:1 input multiplexer with an optional crystal oscillator input, two banks of 4 differential outputs with multi-mode buffers (LVPECL, LVDS, HCSL, or Hi-Z), one LVCMOS output, and 3 independent output buffer supplies ( $V_{CCOA}$ ,  $V_{CCOB}$ ,  $V_{CCOC}$ ). The input selection and output buffer modes are controlled via pin strapping. The device is offered in a 32 pin WQFN package.

### $V_{CC}$ and $V_{CCO}$ Power Supplies

The SiT92216 has separate 3.3/2.5 core ( $V_{CC}$ ) and 3 independent 3.3 V/2.5 V output power supplies ( $V_{CCOA}$ ,  $V_{CCOB}$ ,  $V_{CCOC}$ ). HCSL can support 1.8 V output power supplies ( $V_{CCOA}$ ,  $V_{CCOB}$ ).  $V_{CCOC}$  supply can operate on 3.3 V/2.5 V/1.8 V rail. Output supply operation at 2.5 V enables lower power consumption and output-level compatibility with 2.5 V receiver devices. The output levels for LVPECL ( $V_{OH}$ ,  $V_{OL}$ ) and LVCMOS ( $V_{OH}$ ) are referenced to its respective  $V_{CCO}$  supply, while the output levels for LVDS and HCSL are relatively constant over the specified  $V_{CCO}$  range

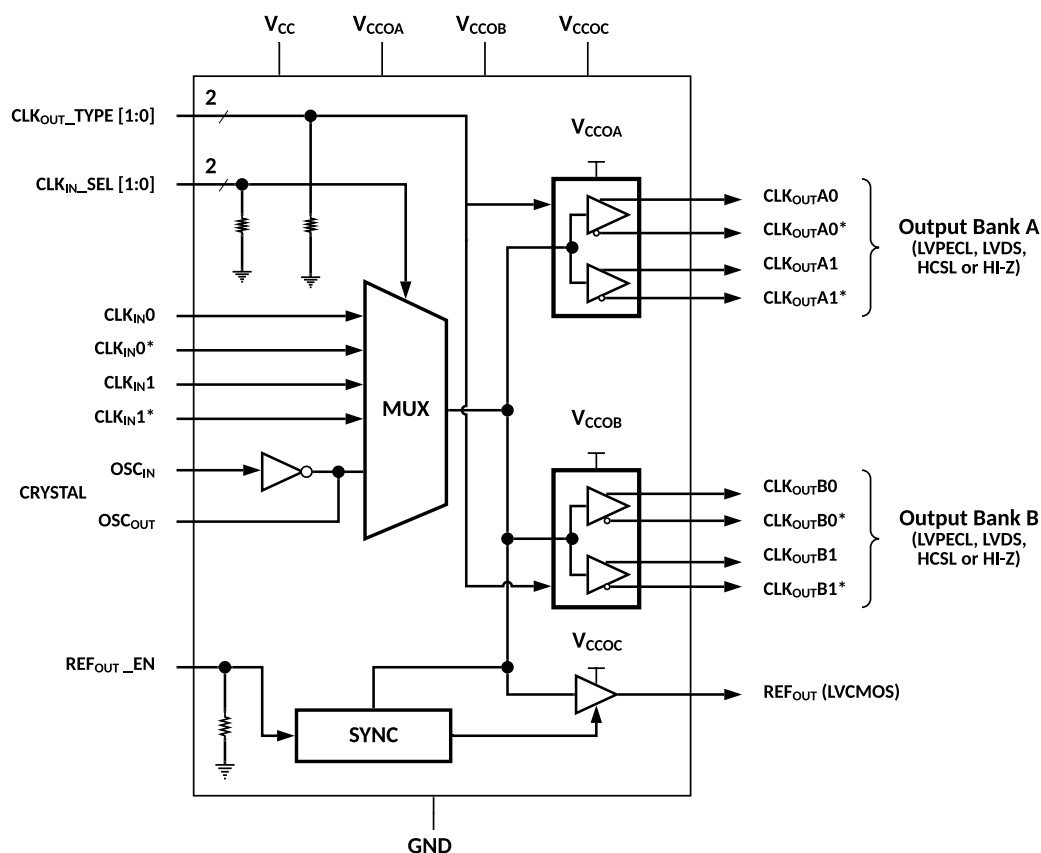


Figure 3. Functional Block Diagram

### Clock Inputs

The input clock can be selected from CLK\_IN0/CLK\_IN0\*, CLK\_IN1/CLK\_IN1\*, or OSC\_IN. Clock input selection is controlled using the CLK\_IN\_SEL[1:0] inputs as shown in Table 18. When CLK\_IN0 or CLK\_IN1 are selected, the oscillator is power down. The user can float OSC\_IN and OSC\_OUT pins, since these pins are internally pulled down. OSC\_IN is pulled down with a 56 K $\Omega$  resistance.

Table 18. Input Clock Selection

CLK_IN_SEL[1]	CLK_IN_SEL[0]	Selected Clock
0	0	CLK_IN0, CLK_IN0*
0	1	CLK_IN1, CLK_IN1*
1	0	Crystal Or Crystal bypass AC coupled mode
1	1	Crystal bypass DC coupled mode

## Clock States (Input vs Output States)

**Table 19. Input versus Output Stages**

State of Selected Clock input	Output State
Inputs are floating	Logic low
Inputs are logic low	logic low
Inputs are logic high	logic high

## Output Driver Type

The differential output buffer type for Bank A and Bank B outputs can be configured using the CLKOUT\_TYPE[1:0] inputs, respectively, as shown Table 20. For applications where all differential outputs are not needed, any unused output pin should be left floating with a minimum copper length to minimize capacitance and potential coupling and reduce power consumption. If an entire output bank will not be used, it is recommended to disable (Hi-Z) the bank to reduce power.

**Table 20. Programming of Output Driver Type**

CLKOUT_TYPE1	CLKOUT_TYPE0	CLK Buffer Type
0	0	LVPECL
0	1	LVDS
1	0	HCSL
1	1	HIZ

## Reference Output

The reference output (REF<sub>OUT</sub>) provides a LVCMOS copy of the selected input clock. The LVCMOS output high level is referenced to the V<sub>CCOC</sub> voltage. REF<sub>OUT</sub> can be enabled or disabled using the enable input pin, REF<sub>OUT\_EN</sub>, as shown in Table 21. The reference output clock is internally synchronized to the selected clock. This avoids any glitches or runt pulses while enabling or disabling the reference clock. Pulling REF<sub>OUT\_EN</sub> to LOW, forces the outputs to the high-impedance state within 4 falling edges of the input signal. The outputs remain in the high-impedance state as long as REF<sub>OUT\_EN</sub> is LOW. When REF<sub>OUT\_EN</sub> goes from HIGH to LOW, the output clock is disabled within 4 falling edges of the input clock signal. The output is disabled at the falling edge of the input clock. This allows to disable the output clock in a glitch free manner.

When REF<sub>OUT\_EN</sub> goes from low to high, the output clock is enabled within a time delay  $t_d$ , where  $t_d$  is given by the following equation.

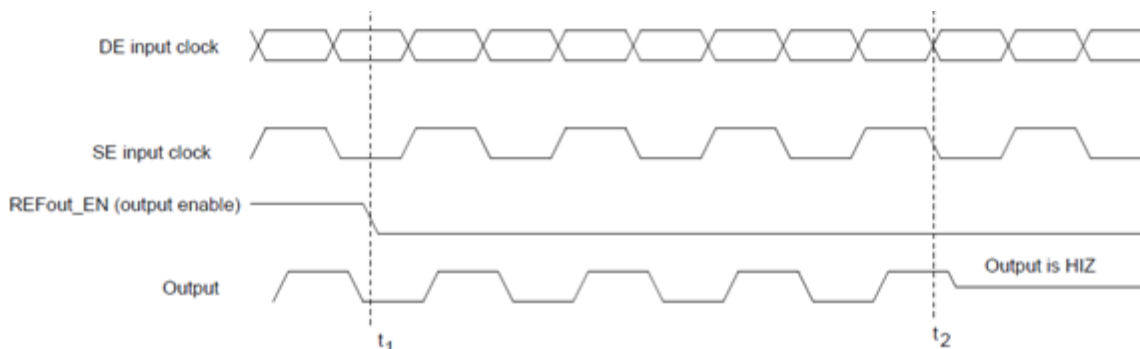
$$t_{d,refout\_en} = 0.5n + 3 * T_{in}.$$

$T_{in}$  is the time period of the input clock.

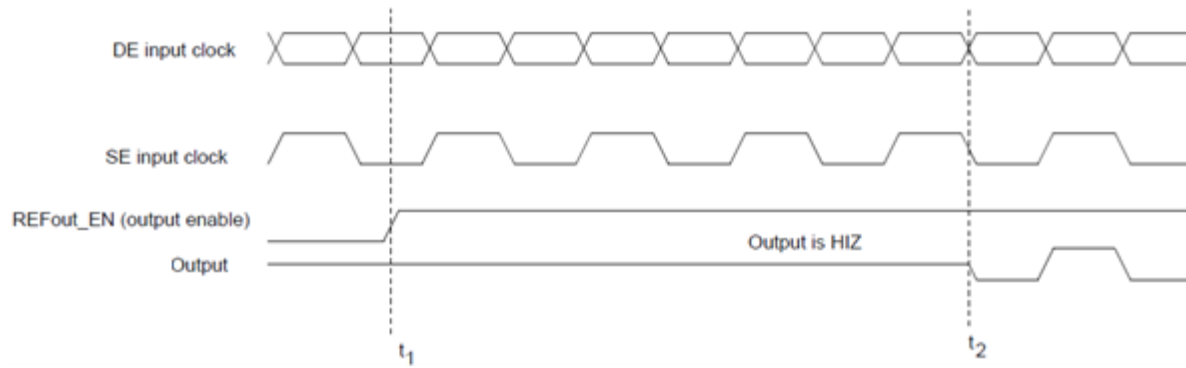
When REF<sub>OUT\_EN</sub> is disabled, the use of a resistive loading can be used to set the output to a predetermined level. For example, if REF<sub>OUT\_EN</sub> is configured with a 1K  $\Omega$  load to ground, then the output will be pulled to low when disabled.

**Table 21. Reference Output Enable**

REF <sub>OUT_EN</sub>	Output State
0	Disabled (HiZ)
1	Enabled



**Figure 4. REF<sub>OUT\_EN</sub>: output disable**

**Figure 5. REF<sub>OUT\_EN</sub>: output enable**

## Application Information

### Current consumption and Power Dissipation Calculations

The current consumption specified in the Electrical Characteristics can be used to calculate the total power dissipation and the IC power dissipation for any output driver configuration. The total current drawn from the  $V_{CC}$  is given by the equation below.

$$I_{CC} = I_{CORE,STATIC} + N * (0.5 * I_{ODRENABLE}) + N * \left(0.5 * \frac{f_{in}}{2.1G}\right) * I_{CORE,DYN}$$

- $I_{CC}$ , is the total core current drawn from  $V_{CC}$ .
- $I_{CORE,STATIC}$ , is the current taken from  $V_{CC}$ , if not clocks are toggling and both the output driver banks are in HIZ state.
- $I_{ODRENABLE}$  is the increment current taken from  $V_{CC}$  if all ODR banks are enabled.
- $I_{CORE,DYN}$ , is the switching current taken from  $V_{CC}$  when the selected input clock is toggling at a frequency of  $f_{in}$ (Hz).
- N is the numebr of output banks enabled.

Current consumed by the output supplies in each mode are listed below. The current in output bank A/B in LVPECL mode is given below.

$$I_{CCOA} = I_{CCOB} = I_{CC\_LVPECL}$$

The current in output bank A/B in LVDS mode is given below.

$$I_{CCOA} = I_{CCOB} = I_{CC\_LVDS}$$

The current in output bank A/B in HCSL mode is given below.

$$I_{CCOA} = I_{CCOB} = I_{CC\_HCSL}$$

The current in output bank C is given below.

$$I_{CCOC} = I_{CC\_LVCMOS}$$

The equation for the total power dissipation is given below.

$$P_{TOTAL} = V_{CC} * I_{VCC} + V_{CCOA} * I_{CCOA} + V_{CCOB} * I_{CCOB} + V_{CCOC} * I_{CCOC}$$

If the output driver configuration is LVPECL or LVDS, then the power dissipated in any termination resistors and termination voltages need to be accounted to calculate the power dissipation in the device.

The power dissipated in the termination resistor in LVPECL mode is given below.

$$P_{RT\_PECL} = \frac{(V_{OH\_PECL} - V_{TT})^2}{R_T} + \frac{(V_{OL\_PECL} - V_{TT})^2}{R_T}$$

The power dissipated in the termination voltage for LVPECL mode is given below

$$P_{VTT\_PECL} = V_{TT} * \left( \frac{(V_{OH\_PECL} - V_{TT})}{R_T} + \frac{(V_{OL\_PECL} - V_{TT})}{R_T} \right)$$

The power dissipated in the ground referenced termination resistor for HCSL is given below.

$$P_{RT\_HCSL} = \frac{V_{OH\_HCSL}^2}{R_T}$$

The power dissipated in the device is given below.

$$P_{DEVICE} = P_{TOTAL} - N_1 * (P_{RT\_PECL} + P_{VTT\_PECL}) - N_2 * P_{RT\_HCSL}$$

where

- N1 is the number of LVPECL output pairs with termination resistors to  $V_{TT}$  (usually  $V_{CCO-2V}$ ).
- N2 is number of HCSL output pairs with termination resistors to GND.

Example: Worst case power dissipation

BANK A and B output drivers are configured in LVPECL mode. The input frequency is 2100 MHz.  $V_{CC} = 3.465$ ,  $V_{CCOA} = V_{CCOB} = V_{CCOC} = 3.465$ ,  $REF_{OUT}$  is enabled. Assume 5 pF load for  $REF_{OUT}$ .

**Table 22. Worst case power dissipation**

Parameter	Value	Unit
$V_{CC}$	3.465	V
$V_{CCOA}$	3.465	V
$V_{CCOB}$	3.465	V
$V_{CCOC}$	3.465	V
$I_{CC}$	49	mA
$I_{CCOA}$	84	mA
$I_{CCOB}$	84	mA
$I_{CCOC}$	10	mA
$P_{TOTAL}$	569	mW
$V_{OH\_PECL}$	2.5	V
$V_{OL\_PECL}$	1.8	V
$V_{TT}$	1.465	V
$P_{RT\_PECL}$	23.6	mW
$P_{VTT\_PECL}$	40	mW
$P_{DEVICE}$	532	mW

## Driving the Clock Inputs

The SiT92216 has two universal clock inputs (CLK<sub>IN0</sub>/CLK<sub>IN0</sub>\* and CLK<sub>IN1</sub>/CLK<sub>IN1</sub>\*). SiT92216 can accept 3.3 V/2.5 V LVPECL, LVDS, CML, SSTL, and other differential and single-ended signals that meet input common mode, slew rate and swing requirements specified in the Electrical Characteristics. The SiT92216 supports a wide common mode voltage range and input signal swing. To achieve the best possible phase noise and jitter performance, it is mandatory for the input to have high slew rate of 3 V/ns (differential) or higher. Driving the input with a lower slew rate will degrade the noise floor and jitter. It is recommended to drive the input signal differentially for better slew rate and jitter. The user can also drive a single ended clock. If the user is driving the single ended clock signal on say CLK<sub>IN0</sub>, then CLK<sub>IN0</sub>\* pin need to be connected to a 0.1 uF capacitor on the PCB.

## Driving Clock Inputs with LVCMOS Driver (AC coupled)

Figure 6 shows how a differential input can be wired to accept LVCMOS single ended levels in AC coupled mode. The bypass capacitor (C1) is used to help filter noise on the DC bias on the inverting pin of the clock input. This bypass

should be located as close to the input pin as possible. Two resistors R<sub>T1</sub> and R<sub>T2</sub> set the common mode voltage at the output of the LVCMOS driver to V<sub>CC</sub>/2. This prevents average DC leakage current from the LVCMOS driver and avoids unnecessary power dissipation.

For example, if the input clock is driven from a single-ended 2.5 V LVCMOS driver and the DC offset (or swing center) of this signal is 1.25 V, the R<sub>T1</sub> and R<sub>T2</sub> values should be adjusted to set the V<sub>I</sub> at 1.25 V. This configuration requires that the sum of the output impedance of the driver (R<sub>o</sub>) and the series resistance (R<sub>s</sub>) equals the transmission line impedance. In addition, matched termination at the input will attenuate the signal in half. This can be done in the following way. First, R<sub>T1</sub> and R<sub>T2</sub> in parallel should equal the transmission line impedance. For most 50 Ω applications, R<sub>T1</sub> and R<sub>T2</sub> can be 100 Ω.

$$Z_o = R_o + R_s = 50 \Omega$$

$$\frac{R_{T1} * R_{T2}}{R_{T1} + R_{T2}} = 50 \Omega$$

$$\frac{V_{CC} * R_{T2}}{R_{T1} + R_{T2}} = \frac{V_{CC}}{2}$$

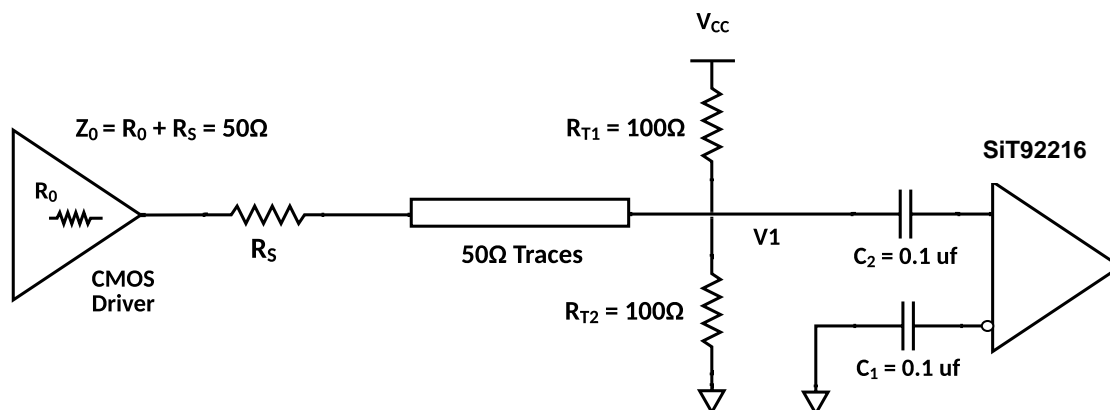


Figure 6. AC coupling LVCMOS clock to SiT92216

The inverting differential input can be connected to a 0.1 uF bypass capacitor. This pin is biased internally to a voltage close to V<sub>CC</sub>/2.

Another variant of the AC coupling of LVCMOS input clock is shown in Figure 7. We use single termination resistor of

50 Ω to ground. A 0.1 uF (C<sub>3</sub>) ac coupling capacitor is connected in series with the LVCMOS clock source to prevent DC leakage current.

$$Z_o = R_o + R_s = 50 \Omega$$

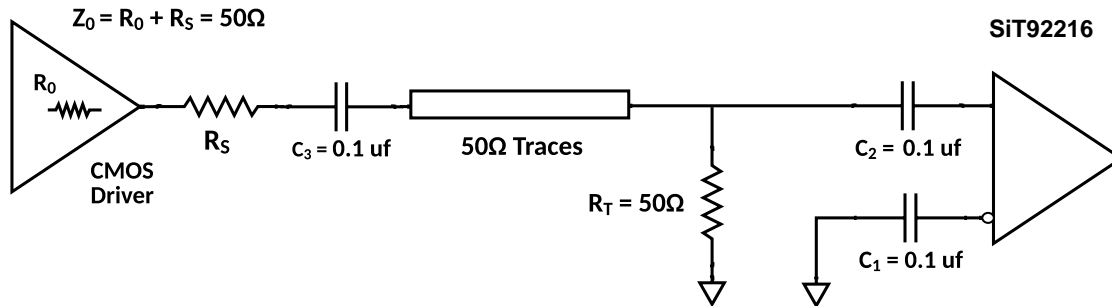


Figure 7. AC coupling of LVCMOS clock with single 50 Ω resistor termination to ground

### Driving Clock Inputs with LVCMOS Driver (DC coupled)

Figure 8 shows how a differential input can be wired to accept LVCMOS single ended clock signals in DC coupled mode. The reference voltage  $V1 = V_{CC}/2$  is generated by the bias resistors  $R_{S1}$  and  $R_{S2}$ . The bypass capacitor ( $C1$ ) is used to help filter noise on the DC bias. This bias circuit should be located as close to the input pin as possible. The ratio of  $R_{S1}$  and  $R_{S2}$  might need to be adjusted to position the bias voltage  $V2$  in the center of the input voltage swing.

$$\frac{V_{CC} * R_{S2}}{R_{S1} + R_{S2}} = \frac{V_{CC}}{2}$$

$$\frac{R_{T1} * R_{T2}}{R_{T1} + R_{T2}} = 50 \Omega$$

$$\frac{V_{CC} * R_{T2}}{R_{T1} + R_{T2}} = \frac{V_{CC}}{2}$$

$$Z_o = R_o + R_s = 50 \Omega$$

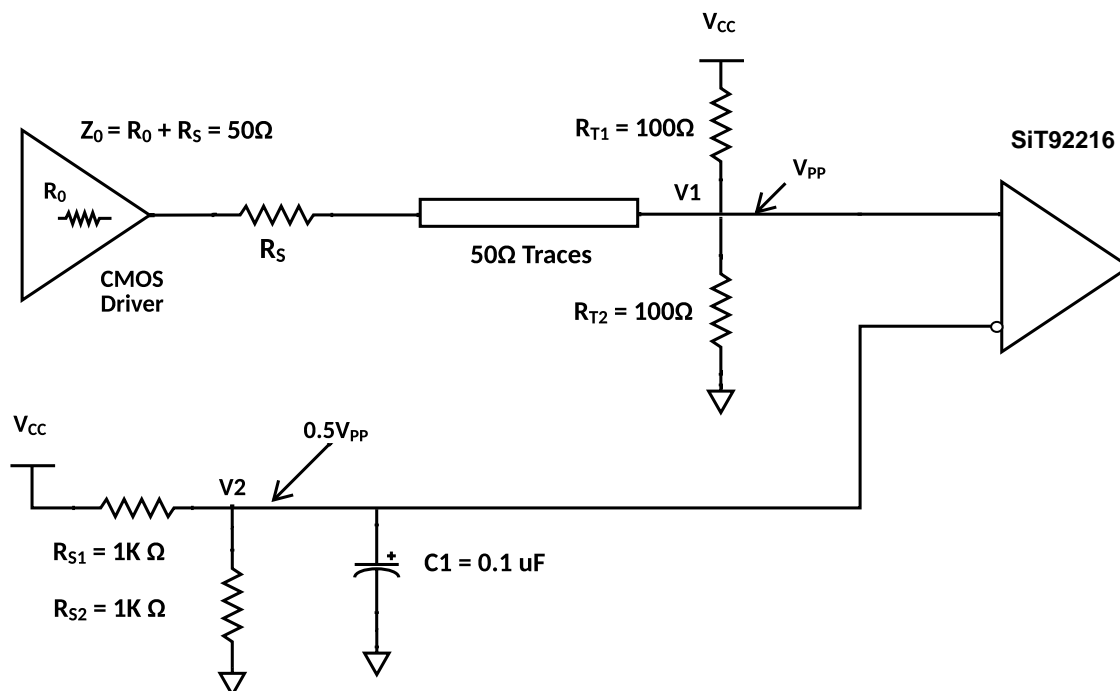


Figure 8. DC coupling of LVCMOS clock to SiT92216 – configuration 1

For example, if the input clock is driven from a single-ended 2.5 V LVCMOS driver and the DC offset (or swing center) of this signal is 1.25 V, the  $R_{S1}$  and  $R_{S2}$  values should be adjusted to set the V2 at 1.25 V. The values below are for when both the single ended swing and  $V_{CC}$  are at the same voltage.

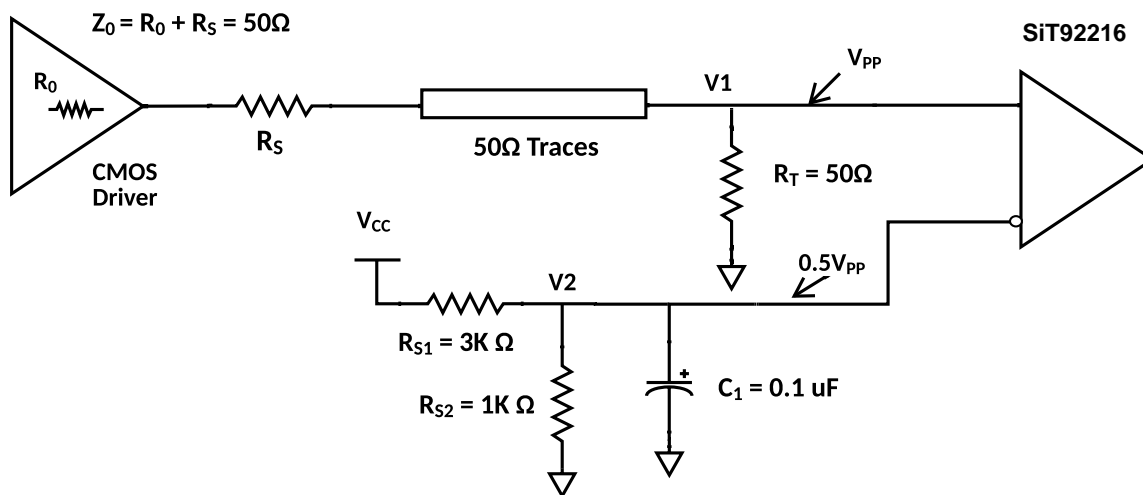
This configuration requires that the sum of the output impedance of the driver ( $R_o$ ) and the series resistance ( $R_s$ ) equals the transmission line impedance. In addition, matched termination at the input will attenuate the signal in half. This can be done in one of two ways. First,  $R_{T1}$  and  $R_{T2}$  in parallel should equal the transmission line impedance. For most 50  $\Omega$  applications,  $R_{T1}$  and  $R_{T2}$  can be 100  $\Omega$ . The

values of the resistors can be increased to reduce the loading for slower and weaker LVCMOS driver.

Figure 9 shows a second input clock configuration where  $R_{T1}$ ,  $R_{T2}$  are removed and replaced with a 50  $\Omega$  termination resistor  $R_T$  to ground. It is possible that LVCMOS driver (or clock source) may not be able to drive 50  $\Omega$  load in DC coupled mode. The user can use series RC termination to overcome this limitation. The design equations for the input clock configuration shown in Figure 9 is given below

$$Z_o = R_o + R_s = 50 \Omega$$

$$\frac{V_{CC} * R_{S2}}{R_{S1} + R_{S2}} = \frac{V_{pp}}{2}$$



**Figure 9. DC coupled LVCMOS input clock configuration – configuration 2**

The LVCMOS single ended clock input with series RC termination near the buffer is shown in Figure 10. There is a single termination resistor  $R_T$  which is connected to ground through a capacitor  $C_{AC}$ .

The value of series capacitor is given by a formula.

$$C_{AC} \geq \frac{3T_D}{50\Omega}$$

$T_D$  is the transmission line delay

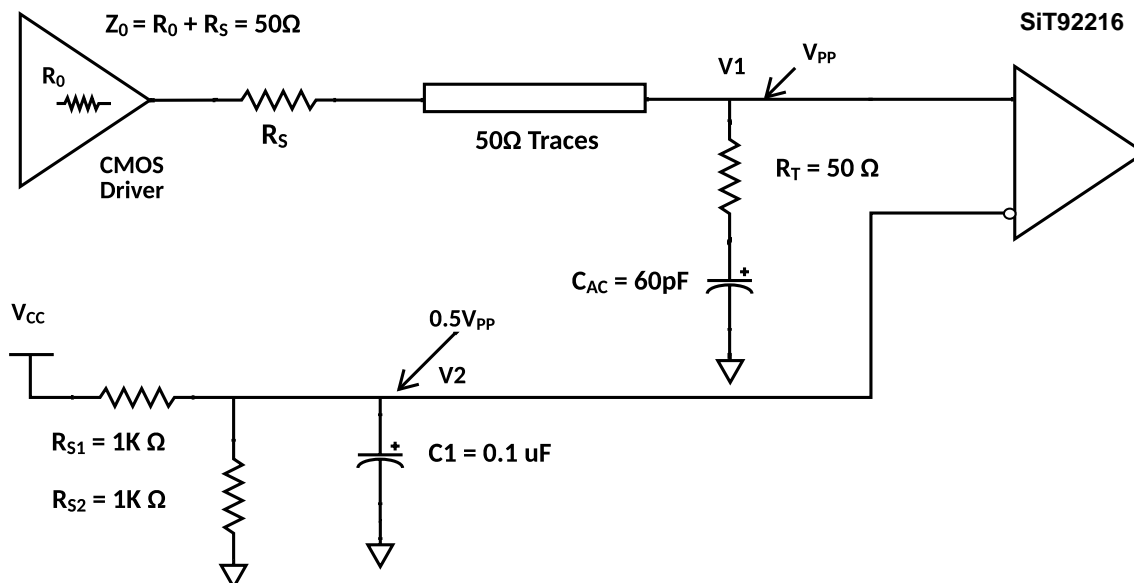


Figure 10. DC coupled LVCMOS input clock with series RC termination – configuration 3

For low frequencies we can direct couple the LVCMOS clock to SiT92216 input clock pin as shown in [Figure 11](#).

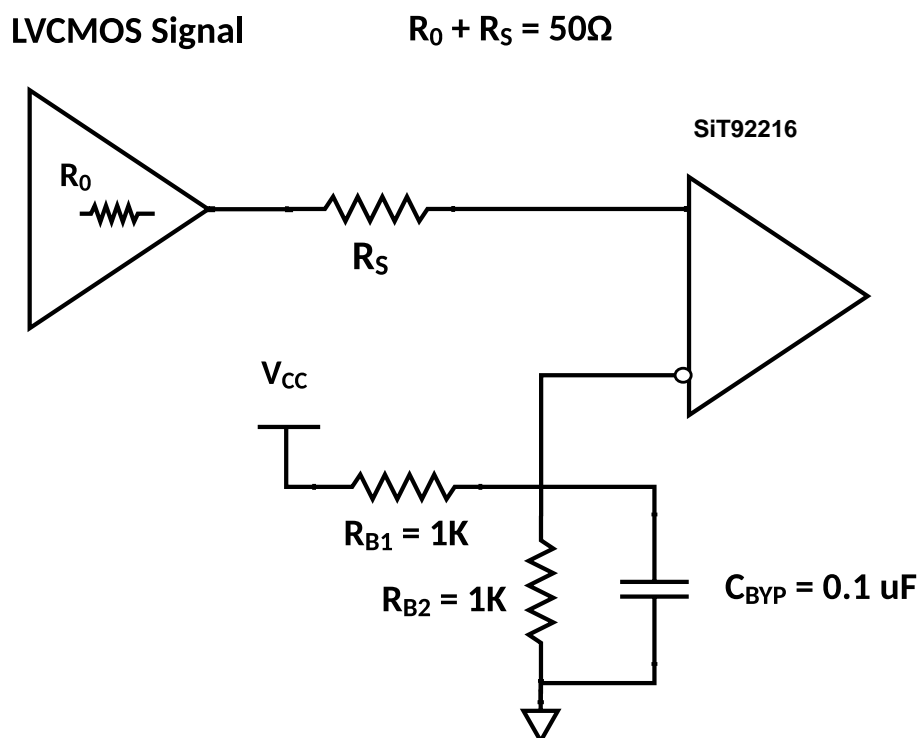


Figure 11. Direct coupling of LVCMOS clock to SiT92216

### Driving OSC\_IN with LVCMOS Driver (AC coupled)

The crystal input OSC\_IN can be overdriven with single ended clock (LVCMOS driver or one side of a differential driver). The peak swing at OSC\_IN should be limited to 1.5 V. The OSC\_OUT pin, in this case can be floating. The SEL1, SEL0 should be 2'b10. The maximum voltage at OSC\_IN should not exceed 1.5 V and minimum voltage should not go below -0.3 V. The slew rate at OSC\_IN should be greater than 0.2 V/ns.

For 3.3 V LVCMOS inputs, the amplitude must be reduced from full swing to at least half the swing in order to prevent signal interference with the power rail and to reduce internal noise. Figure 12 shows an example of the interface diagram for a high speed 3.3 V LVCMOS driver. This configuration requires that the sum of the output impedance of the driver ( $R_o$ ) and the series resistance ( $R_s$ ) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This can be

done in one of two ways. First,  $R_{T1}$  and  $R_{T2}$  in parallel should equal the transmission line impedance. For most 50  $\Omega$  applications,  $R_{T1}$  and  $R_{T2}$  can be 100  $\Omega$ .

$$Z_o = R_o + R_s = 50 \Omega$$

$$\frac{R_{T1} * R_{T2}}{R_{T1} + R_{T2}} = 50 \Omega$$

$$\frac{V_{CC} * R_{T2}}{R_{T1} + R_{T2}} = \frac{V_{CC}}{2}$$

For both the AC coupled configurations, the maximum peak to peak swing before the ac coupling capacitor is 1.65 V. The maximum DC bias voltage of OSC\_IN is 0.675 V. Therefore the maximum swing at the OSC\_IN pin is given by the equation given below.

$$V_{swing,pk,XTAL\_IN} = 0.675 + 0.5 * 1.65 = 1.5 V$$

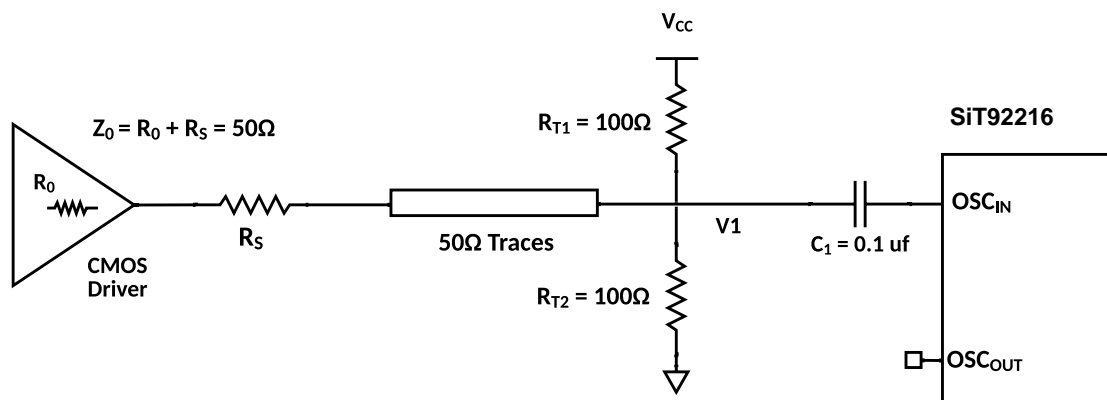


Figure 12. Single ended LVCMOS input – configuration 1, AC coupling to crystal input

Figure 13 shows a second input clock configuration where  $R_{T1}$ ,  $R_{T2}$  are removed and replaced with a 50  $\Omega$  termination

resistor  $R_T$  to ground. A 0.1  $\mu$ F is in series with the CMOS driver to prevent any DC leakage current.

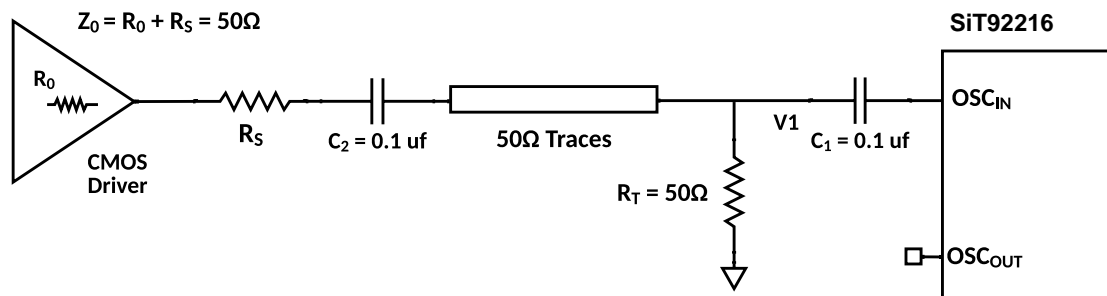


Figure 13. Single ended LVCMOS input – configuration 2, AC coupling to crystal input

**Driving OSC\_IN with LVCMOS Driver (DC coupled)**

The crystal input OSC\_IN can be overdriven with single ended clock as shown in Figure 14, in DC couple mode. The peak swing at OSC\_IN should be limited to 1.5 V

(voltage at the crystal input pin). The OSC\_OUT pin, in this case can be floating. The SEL1, SEL0 should be 2'b11. If the LVCMOS driver is on higher supply, say 3.3 V, use a resistor divider on the PCB to scale down the peak output voltage to 1.5 V.

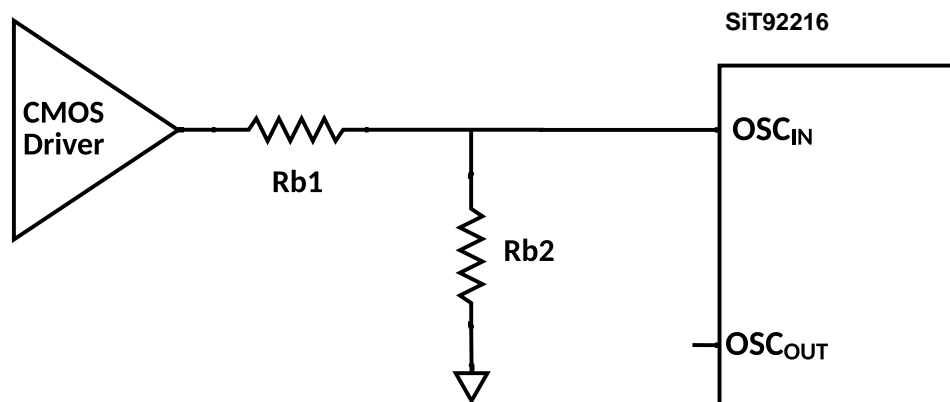


Figure 14. Single ended LVCMOS input, DC coupling to crystal input

**LVDS (DC coupled)**

Terminate with a differential 100  $\Omega$  as close to the receiver as possible. This is shown in Figure 15.

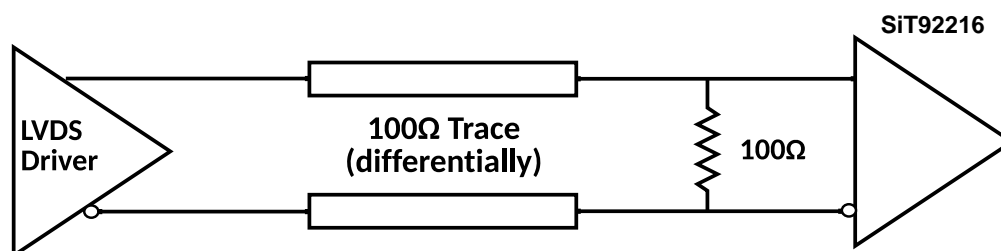
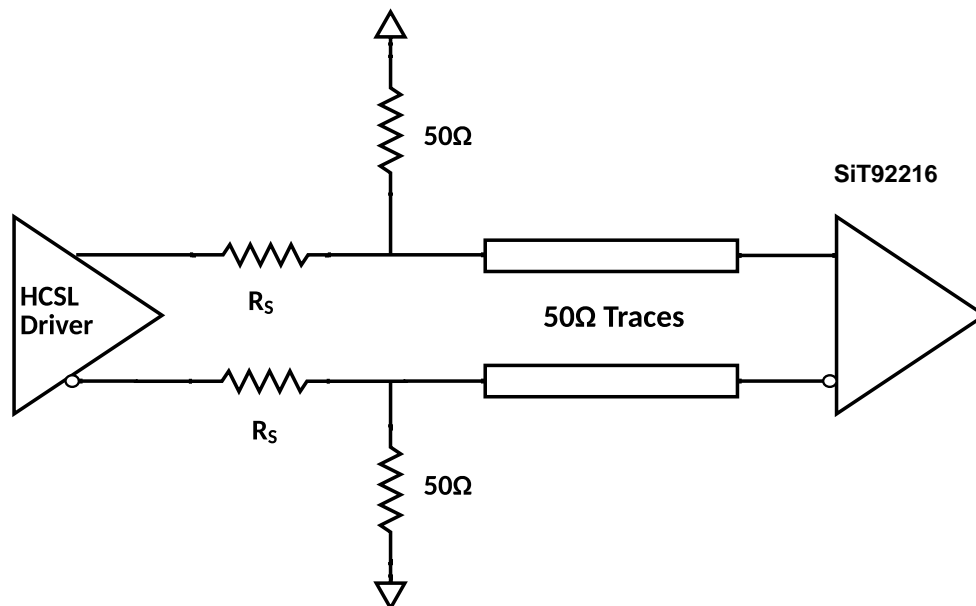


Figure 15. Termination scheme for DC coupled LVDS

**HCSL (DC coupled)**

Termination resistor is 50  $\Omega$  to ground, close to the output driver. A series resistance  $R_s$  is sometimes used to limit the overshoot during fast transients. The termination scheme is shown in [Figure 16](#).



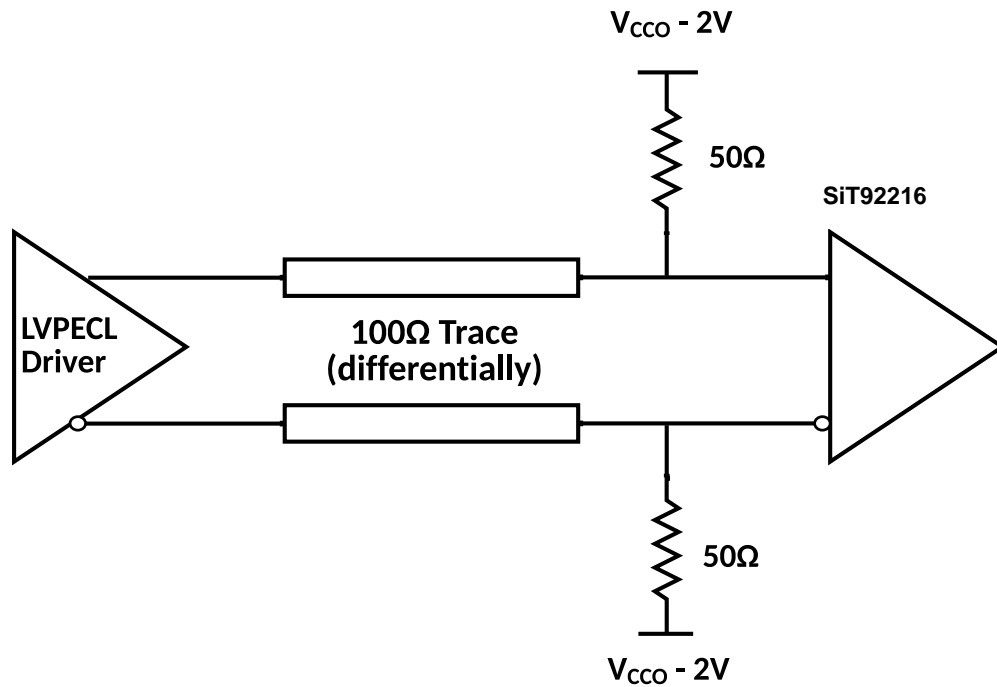
**Figure 16. Termination scheme for DC coupled HCSL**

**LVPECL (DC coupled)**

For DC couple operation, the 50  $\Omega$  termination resistors are placed close to the receiver. The termination resistors are biased with a voltage source  $V_{TT}$ .

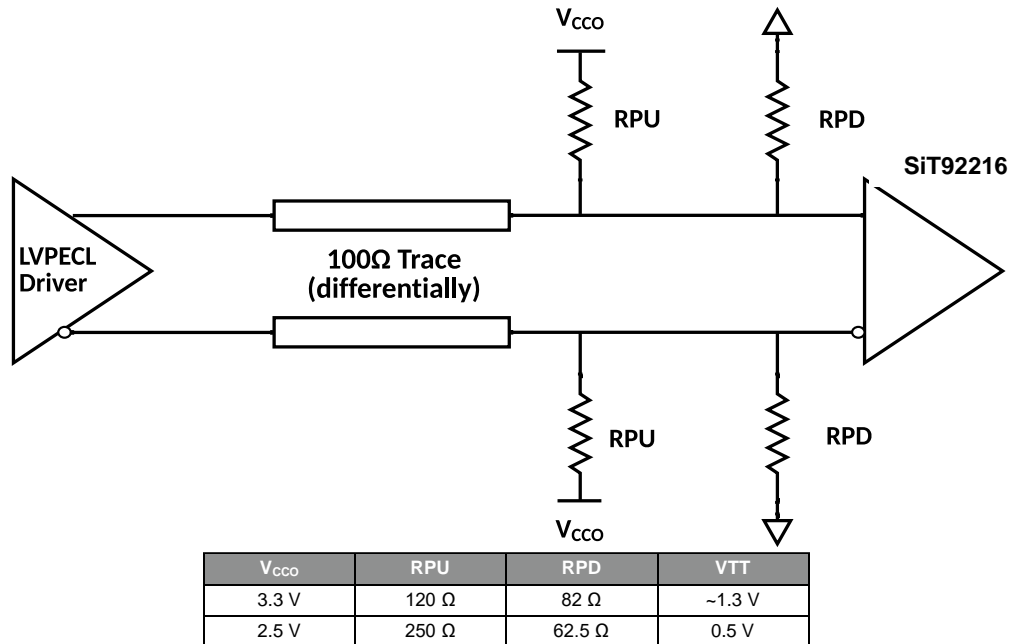
$$V_{TT} = V_{DDO} - 2V.$$

This termination scheme is shown in [Figure 17](#), the user can also implement a Thevenin equivalent of  $V_{TT}$  using a resistor divider. This scheme and the values of the resistors in the resistor divider are given in [Figure 18](#).



$V_{CCO}$	RPU	RPD	VTT
3.3 V	120 Ω	82 Ω	~1.3 V
2.5 V	250 Ω	62.5 Ω	0.5 V

Figure 17. Termination scheme for DC coupled LVPECL



$V_{CCO}$	RPU	RPD	VTT
3.3 V	120 Ω	82 Ω	~1.3 V
2.5 V	250 Ω	62.5 Ω	0.5 V

Figure 18. Termination scheme for DC coupled LVPECL, Thevenin equivalent

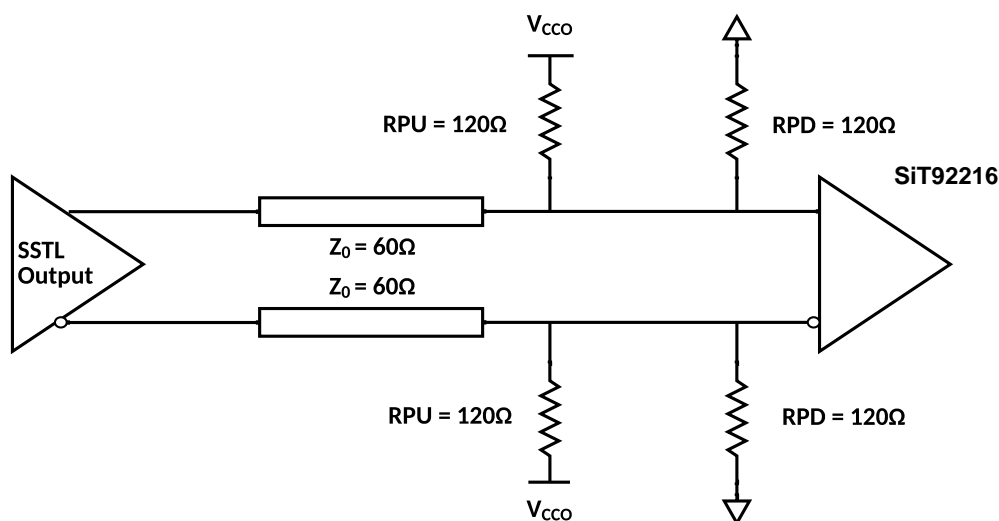
The design equations for the LVPECL Thevenin equivalent termination are given below.

$$\frac{R_{PD} * R_{PU}}{R_{PD} + R_{PU}} = 50\Omega$$

$$\frac{R_{PD} * V_{CCO}}{R_{PD} + R_{PU}} = V_{CCO} - 2V$$

### SSTL (DC coupled)

The SSTL input clock configuration is shown in [Figure 19](#). The transmission line impedance is  $60\Omega$  in the application example given. Therefore we use two  $120\Omega$  resistors from  $V_{CCO}$  to ground for biasing the clock input pins. The effective termination impedance in this case is  $60\Omega$

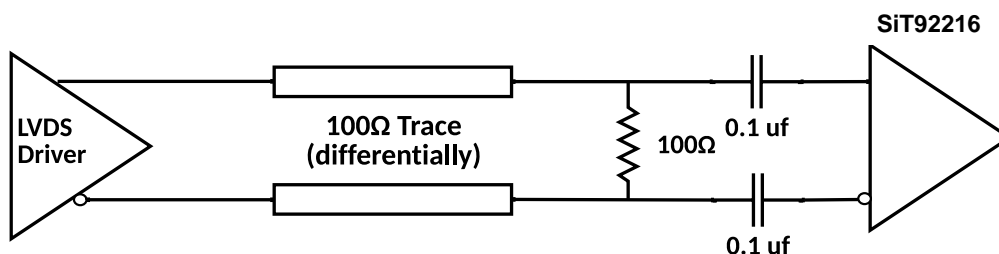


**Figure 19. Example of input clock termination for SSTL clock.**

### LVDS (AC coupled)

The load termination resistor should be placed before the AC coupling capacitors. The load termination resistor and

the AC coupling capacitors should be placed close to the receiver. The termination scheme is shown in [Figure 20](#)

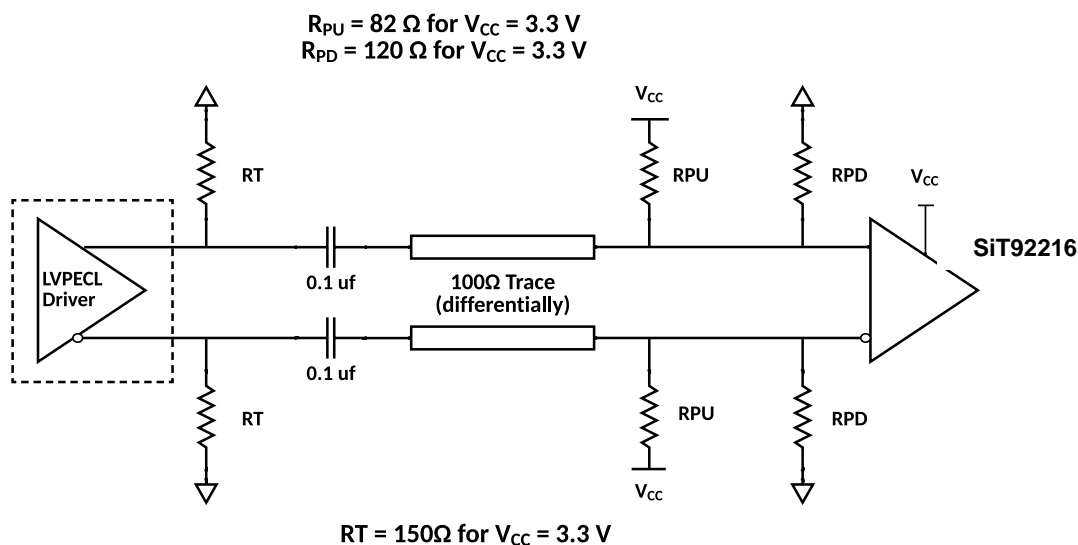


**Figure 20. Termination scheme for AC coupled LVDS**

**LVPECL (AC coupled)**

The LVPECL should have a DC path to ground. So, the user must place a resistance  $R_T$ , close to the output driver. The

LVPECL AC coupling and Thevenin equivalent VTT termination scheme is shown in [Figure 21](#)



**Figure 21. Termination scheme for AC coupled LVPECL, Thevenin Equivalent**

The pull up resistance  $R_{PU}$  and pull down resistance  $R_{PD}$  sets the input common mode voltage for SiT92216. The value of the input common mode voltage can be estimated by the equation given below

$$V_{ICM} = \frac{V_{CC} * R_{PD}}{R_{PU} + R_{PD}} = \frac{3.3 * 120}{120 + 82} = 1.961V$$

The differential input common mode specification of SiT92216 (from data sheet) is  $V_{CC} - 1.1 = 2.2 V$ , therefore the input common mode set by LVPECL AC coupled

termination meets the SiT92216 input common mode specification.

The LVPECL driver chip has resistance  $R_T$  providing DC path for the output driver current in the LVPECL driver. The effective load impedance at the input side of SiT92216 (receiver side) is formed by parallel combination of  $R_{PU}$ ,  $R_{PD}$ .

The effective termination resistor value is given by the equation below

$$R_{termination} = \frac{R_{PU} * R_{PD}}{R_{PU} + R_{PD}} = \frac{120 * 82}{120 + 82} = 48.7 \Omega$$

## Termination of Output Driver of SiT92216 for Various Load Configurations

### SiT92216 REF<sub>OUT</sub> Termination for AC Coupled mode

AC coupling of SiT92216 LVCMOS output driver is shown in [Figure 22](#). We use single termination resistor of  $50 \Omega$  to ground. A  $0.1 \mu F$  AC coupling capacitor is connected in series with the LVCMOS clock source to prevent DC leakage current. The receiver side is terminated with a single  $50 \Omega$  resistance to ground. The clock signal is then

AC coupled to the receiver, in this example.  $C_1$  is a bypass capacitor that is used to suppress noise on the inverting differential input of the receiver.

$$Z_o = R_o + R_s = 50 \Omega$$

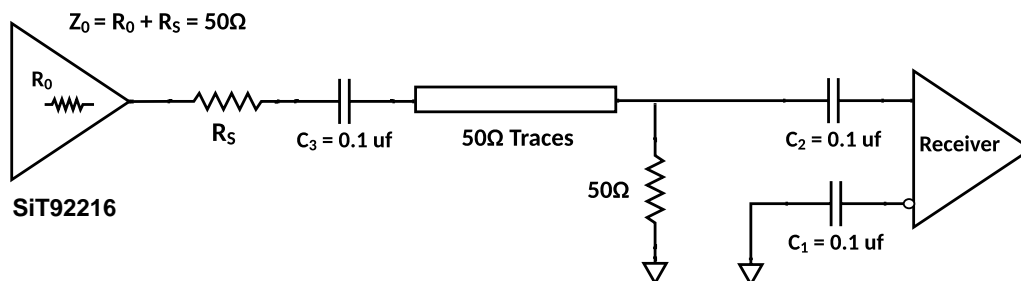


Figure 22. AC coupling of LVCMOS clock with single 50 Ω resistor termination to ground

### SiT92216 REF<sub>OUT</sub> Termination for DC Coupled mode

Figure 23 shows how SiT92216 LVCMOS output drive can be terminated to send clock signals in DC coupled mode. The reference voltage  $V1 = V_{CC}/2$  is generated by the bias resistors  $R_{S1}$  and  $R_{S2}$ . The bypass capacitor ( $C1$ ) is used to help filter noise on the DC bias. This bias circuit should be located as close to the input pin as possible. The ratio of  $R_{S1}$  and  $R_{S2}$  might need to be adjusted to position the bias voltage  $V2$  in the center of the input voltage swing.

$$Z_o = R_o + R_s = 50 \Omega$$

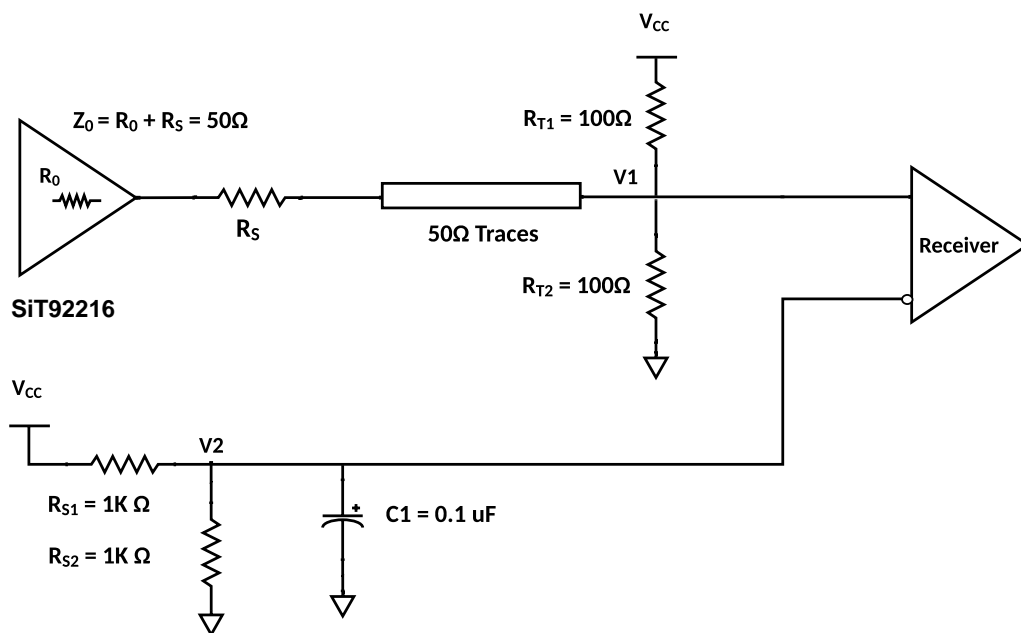


Figure 23. DC coupling of LVCMOS output clock termination – configuration 1

For example, if the SiT92216 supply is 2.5 V then the DC offset (or swing center) of this signal is 1.25 V, the  $R_{S1}$  and  $R_{S2}$  values should be adjusted to set the  $V2$  at 1.25 V. The values below are for when both the single ended swing and  $V_{CC}$  are at the same voltage.

This configuration requires that the sum of the output impedance of the driver ( $R_o$ ) and the series resistance ( $R_s$ )

equals the transmission line impedance. In addition, matched termination at the input will attenuate the signal in half. This can be done in one of two ways. First,  $R_{T1}$  and  $R_{T2}$  in parallel should equal the transmission line impedance. For most 50 Ω applications,  $R_{T1}$  and  $R_{T2}$  can be 100 Ω. The values of the resistors can be increased to reduce the loading for slower and weaker LVCMOS driver.

Figure 24 shows a second input clock configuration where  $R_{T1}$ ,  $R_{T2}$  are removed and replaced with a  $50\ \Omega$  termination resistor  $R_T$  to ground. There will be DC leakage current from SiT92216, for the output termination shown in Figure 24. The user can use series RC termination to overcome this limitation. The design equations for the input clock configuration shown in Figure 24 is given below

$$Z_o = R_o + R_s = 50\ \Omega$$

$$\frac{V_{CC} * R_{S2}}{R_{S1} + R_{S2}} = \frac{V_{pp}}{2} = \frac{V_{CC}}{4}, \text{ Typical value of } R_{S1} = 3K\Omega, R_{S2} = 1K\Omega$$

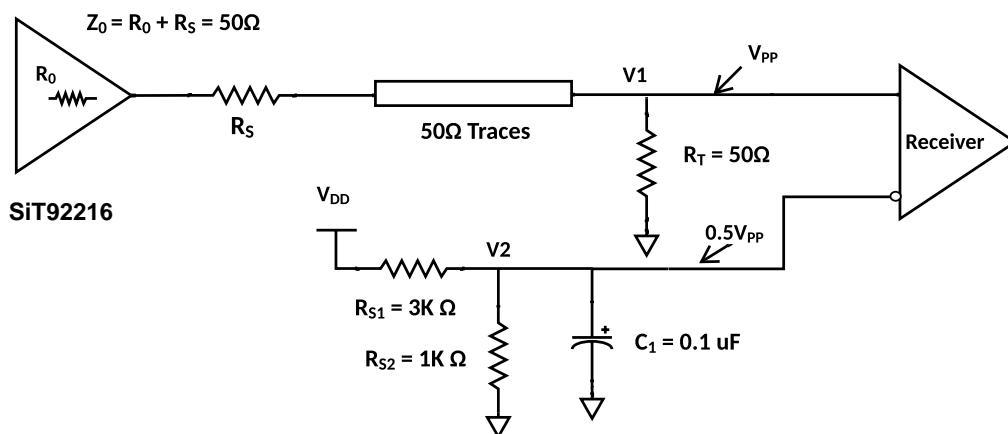


Figure 24. DC coupled LVCMOS output clock configuration – configuration 2

The SiT92216 LVCMOS output driver termination with series RC termination near the buffer is shown in Figure 25. There is a single termination resistor  $R_T$  which is connected to ground through a capacitor  $C_{AC}$ . The value of series capacitor is given by a formula.

$$C_{AC} \geq \frac{3T_D}{50\Omega}$$

$T_D$  is the transmission line delay  
Typical value for  $C_{AC}$  is 60 pF, assuming delay of  $T_D = 200$  ps/inch and 5 inch input clock route length.

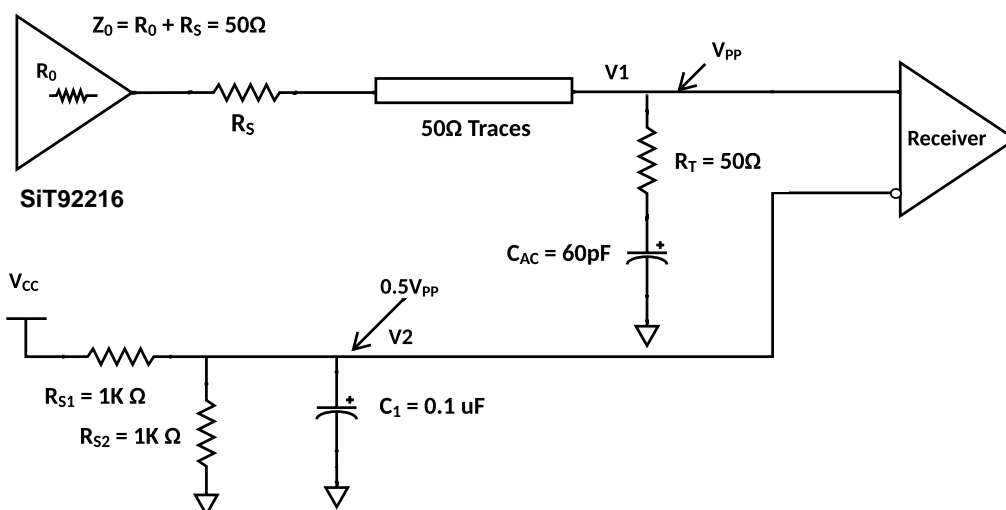


Figure 25. DC coupled LVCMOS output clock with series RC termination – configuration 3

The typical value of  $R_{S1}$  and  $R_{S2}$  in this case is  $1K\ \Omega$  and that of  $C_{AC}$  is 60 pF.

**CMOS (Capacitive load)**

The capacitive load can be driven as shown in [Figure 26](#). For SiT92216 LVCMOS driver the  $R_O$  is very close to  $50\ \Omega$  by design. Therefore  $R_S = 0\ \Omega$  is recommended.

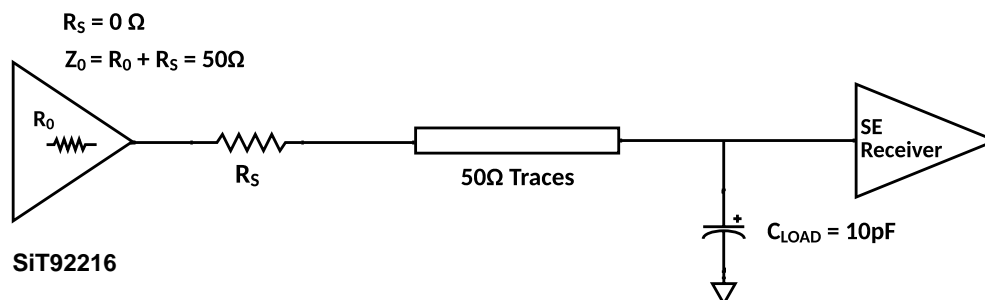


Figure 26. Typical application load

**Termination of Output Drivers (DC coupled)****LVDS DC Coupled Output Termination**

Terminate with a differential  $100\ \Omega$  as close to the receiver as possible. This is shown in [Figure 27](#).

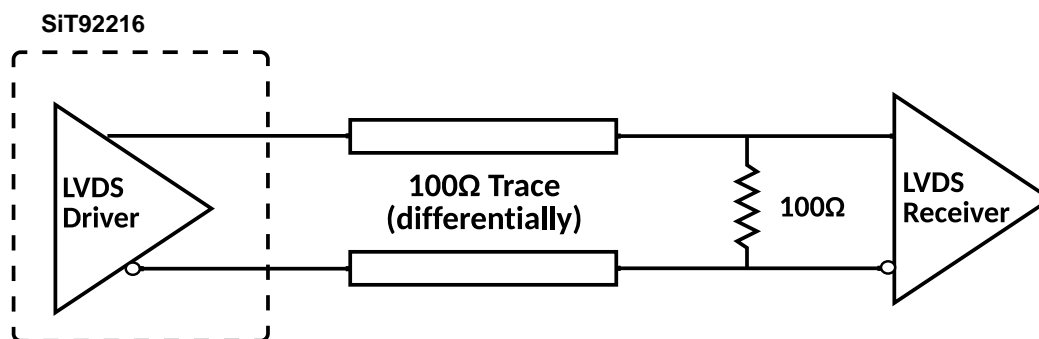
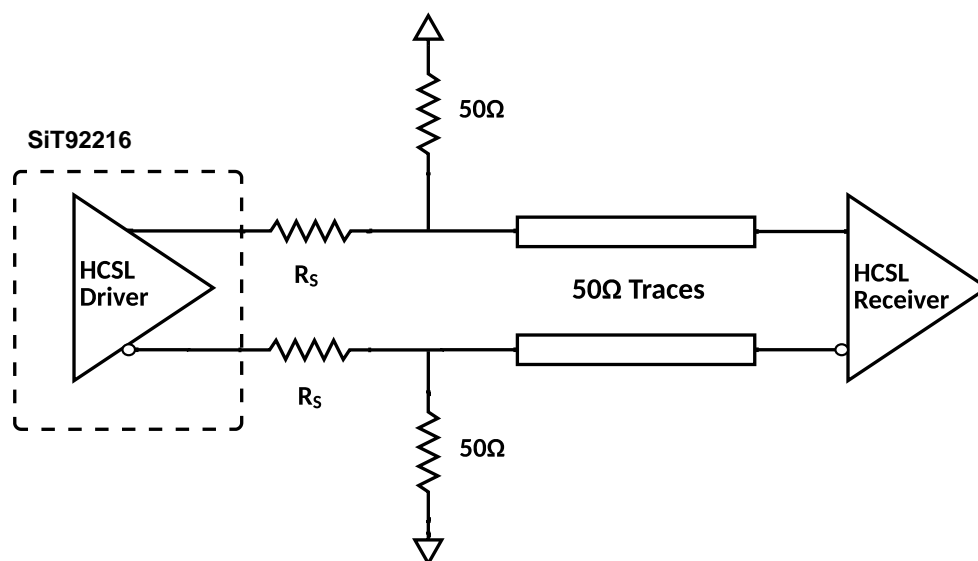


Figure 27. Termination scheme for DC coupled LVDS

**HCSL DC Coupled Output Termination**

Termination resistor is 50  $\Omega$  to ground, close to the output driver. A series resistance  $R_S$  is sometimes used to limit the

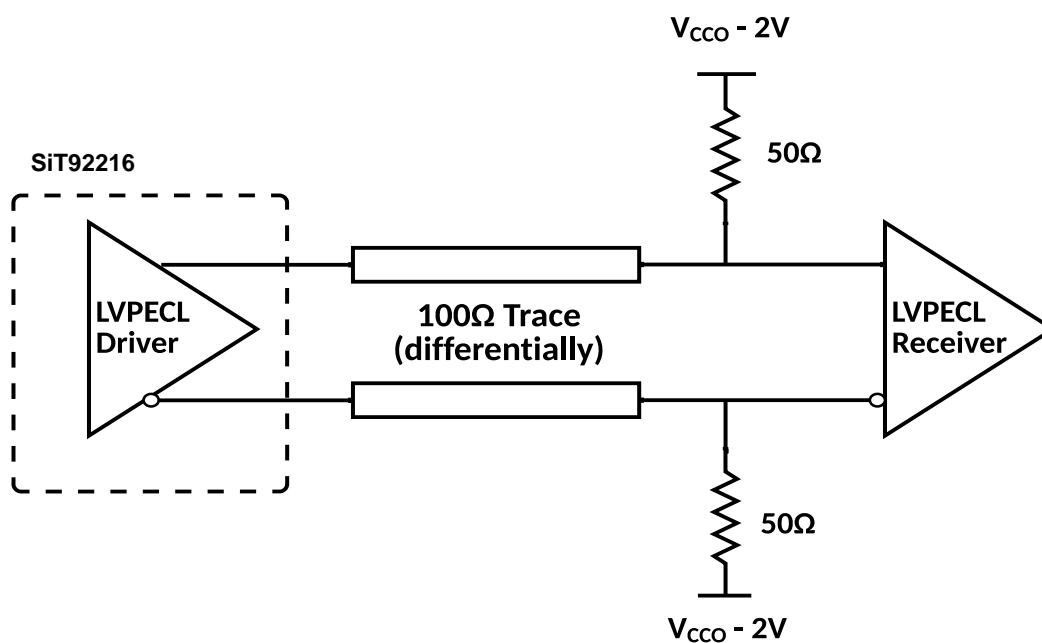
overshoot during fast transients. The termination scheme is shown in [Figure 28](#)



**Figure 28. Termination scheme for DC coupled HCSL**

**LVPECL DC Coupled Output Termination**

For DC couple operation, the 50  $\Omega$  termination resistors are placed close to the receiver. The termination resistors are biased with a voltage source  $V_{TT}$ . Typically,  $V_{TT} = V_{CCO} - 2V$ . This termination scheme is shown in [Figure 29](#)



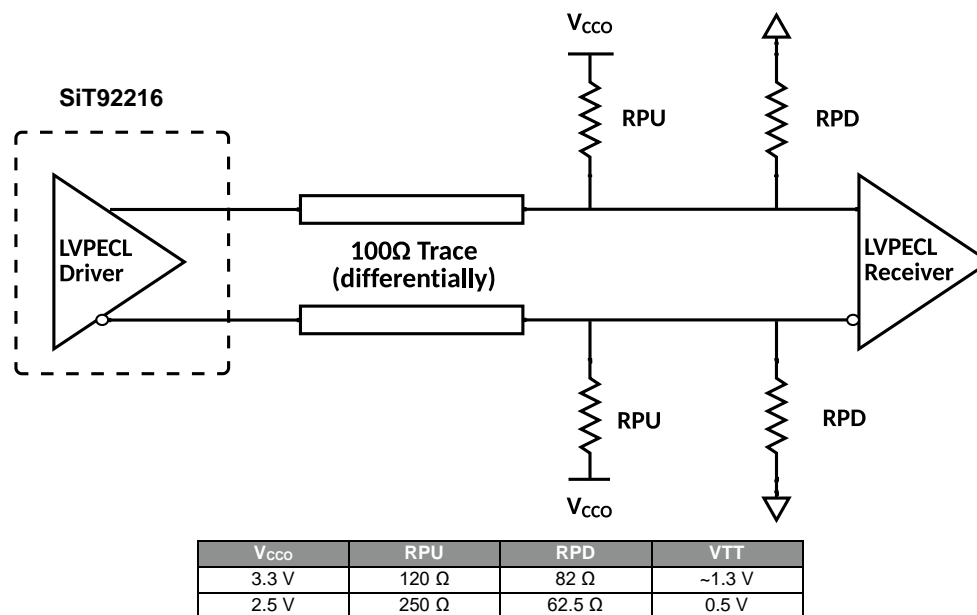
$V_{CCO}$	RPU	RPD	$V_{TT}$
3.3 V	120 $\Omega$	82 $\Omega$	~1.3 V
2.5 V	250 $\Omega$	62.5 $\Omega$	0.5 V

**Figure 29. Termination scheme for DC coupled LVPECL**

Alternatively, the user can also implement a Thevenin equivalent of VTT using a resistor divider. This scheme and the values of the resistors in the resistor divider are given in [Figure 30](#)

$$\frac{R_{PD} * R_{PU}}{R_{PD} + R_{PU}} = 50\Omega$$

$$\frac{R_{PD} * V_{CCO}}{R_{PD} + R_{PU}} = V_{CCO} - 2V$$

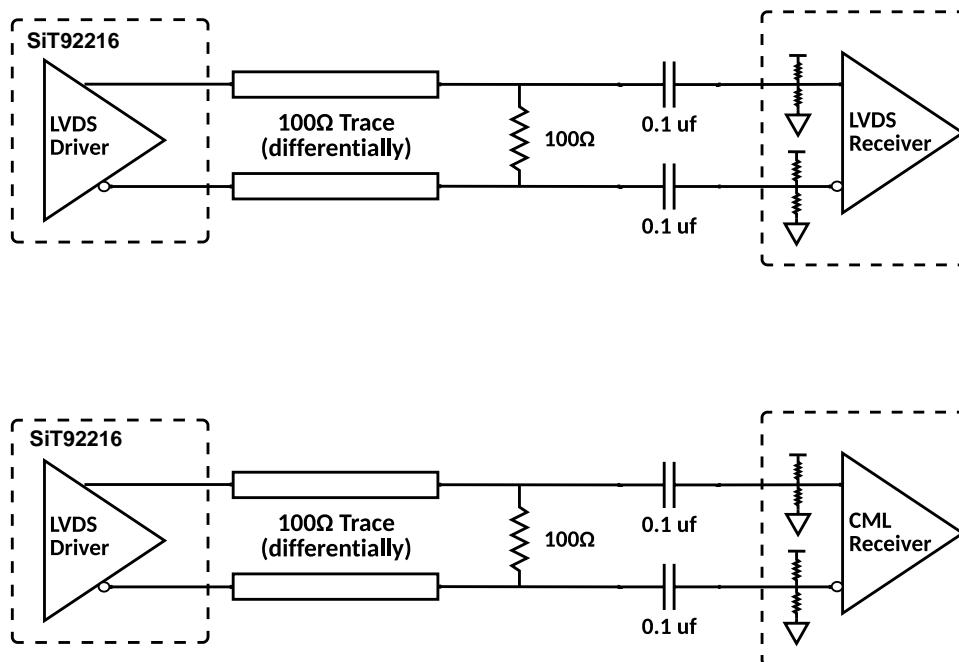


**Figure 30. Termination scheme for DC coupled LVPECL, Thevenin equivalent**

**Termination of Output Drivers (AC coupled)****LVDS AC Coupled Output Termination**

The load termination resistor should be placed before the AC coupling capacitors. The load termination resistor and the AC coupling capacitors should be placed close to the receiver. The termination scheme is shown in [Figure 31](#).

First figure shows SiT92216 output driver configured in LVDS mode. The receiver in this case is shown as LVDS receiver. The second figure shows SiT92216 output driver configured in LVDS mode and the receiver in this case is shown as CML receiver. As long as the LVDS swing is okay with the receiver the AC coupled output termination is same.



**Figure 31. Termination scheme for AC coupled LVDS, driving LVDS receiver and CML receiver**

### LVPECL AC Coupled Output Termination

The LVPECL should have a DC path to ground. So the user must place a resistance  $R_T$ , close to the output driver. The LVPECL AC coupling and Thevenin equivalent  $V_{TT}$

termination scheme is shown in Figure 32. SiT92216 swing reduces by about 20% as the effective load resistor is now the parallel combination of  $R_T$  at the driver side and  $50\ \Omega$  at the receiver side.

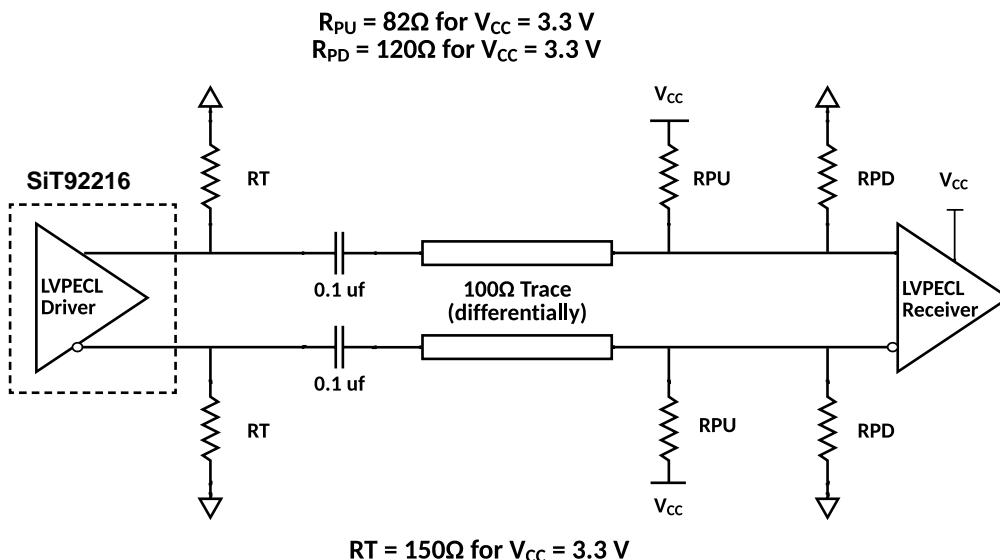


Figure 32. Termination scheme for AC coupled LVPECL, Thevenin Equivalent

The pull up resistance  $R_{PU}$  and pull down resistance  $R_{PD}$  sets the input common mode voltage for LVPECL receiver. The value of the input common mode voltage can be estimated by the equation given below

$$V_{ICM} = \frac{V_{CC} * R_{PD}}{R_{PU} + R_{PD}} = \frac{3.3 * 120}{120 + 82} = 1.961V$$

The LVPECL driver of SiT92216 has resistance  $R_T$  providing DC path for the output driver current in the LVPECL driver. The effective load impedance at the receiver side is formed by parallel combination of  $R_{PU}$ ,  $R_{PD}$ . The effective termination resistor value is given by the equation below

$$R_{termination} = \frac{R_{PU} * R_{PD}}{R_{PU} + R_{PD}} = \frac{120 * 82}{120 + 82} = 48.7\Omega$$

### Termination of Output Drivers in LVPECL Mode, Single Ended, DC coupled

Single ended LVPECL operation is possible. The user can use a balun to convert differential output to single ended output. It is also possible to use the LVPECL driver as one or two separate 700 mV - PP signal. The unused output need to be terminated close to the output driver. These termination schemes are shown in Figure 33 and Figure 34.

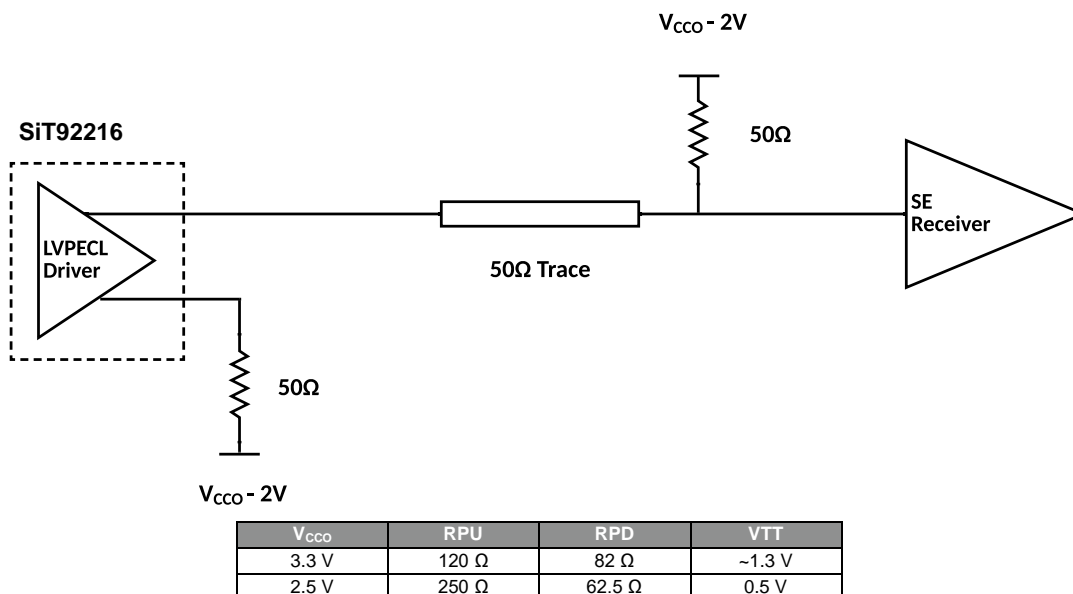


Figure 33. Termination scheme for DC coupled LVPECL, single ended

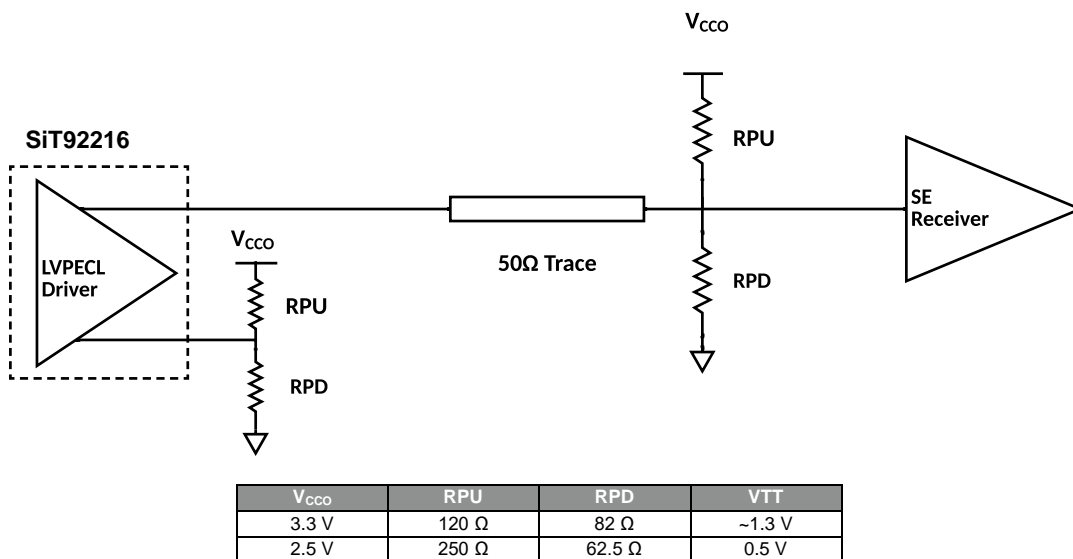


Figure 34. Termination scheme for DC coupled LVPECL, single ended, Thevenin equivalent

### Termination of Output Drivers in LVPECL Mode, Single Ended, AC coupled

LVPECL output driver needs a DC path to ground from its output. Therefore 160  $\Omega$  (if  $V_{CC} = 3.3$  V) resistor to ground is connected from the output of the LVPECL driver to ground. If  $V_{CC} = 2.5$  V, the DC path resistance should be 91  $\Omega$ . The 50  $\Omega$  load termination resistor must be placed close to input receiver and biased to a suitable voltage.

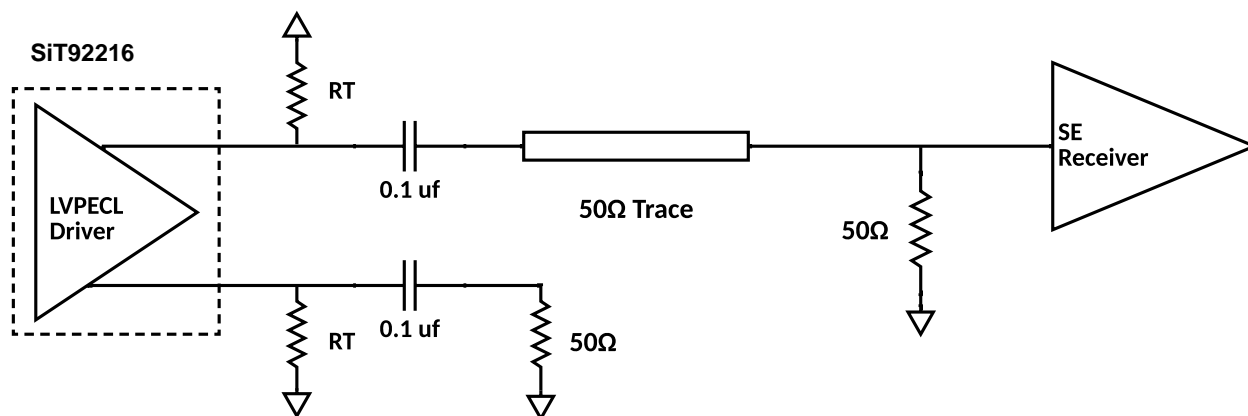


Figure 35. Termination scheme for AC coupled LVPECL, single ended

### Termination of Output Drivers in AC coupled HCSL mode

Termination resistor is 50  $\Omega$  to ground, close to the output driver. A series resistance  $R_s$  is sometimes used to limit the overshoot during fast transients. AC coupling capacitor of 0.1  $\mu\text{F}$  is used to couple the output HCSL signal in to the receiver. The same termination can be used for CML receiver.

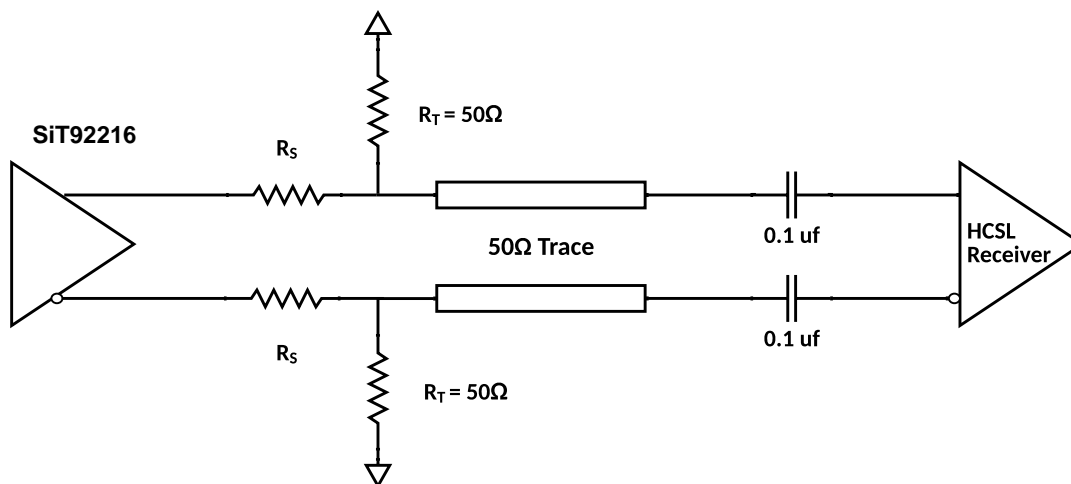


Figure 36. Output driver termination in HCSL AC coupled mode

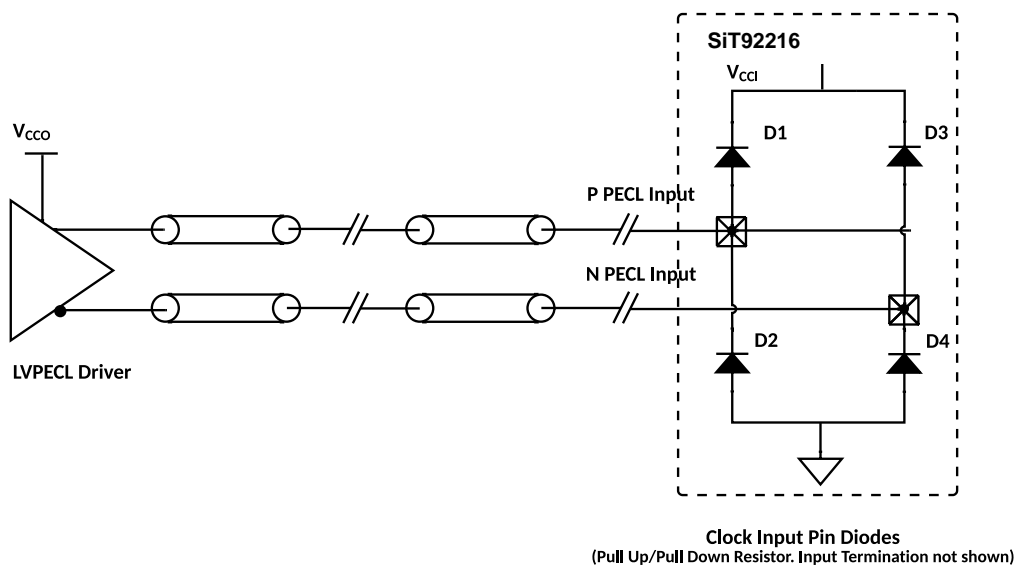
## Hot Swap Recommendations

### Introduction

Hot-swap is a term used to refer to the insertion and removal of a daughter card from a backplane without powering down the system power. With today's high speed data and redundancy requirements, many systems are required to run continuously without being powered down. If special considerations are not taken, the device can be damaged.

### Typical Differential Input Clock

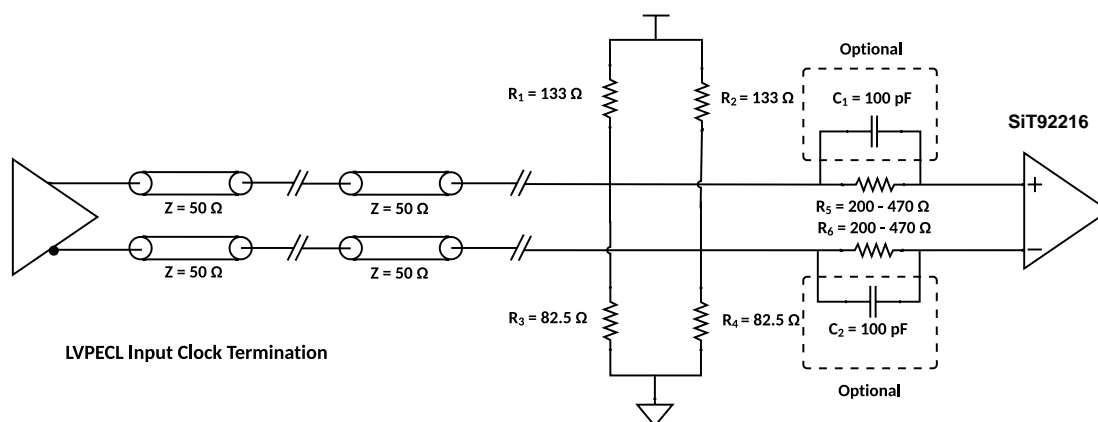
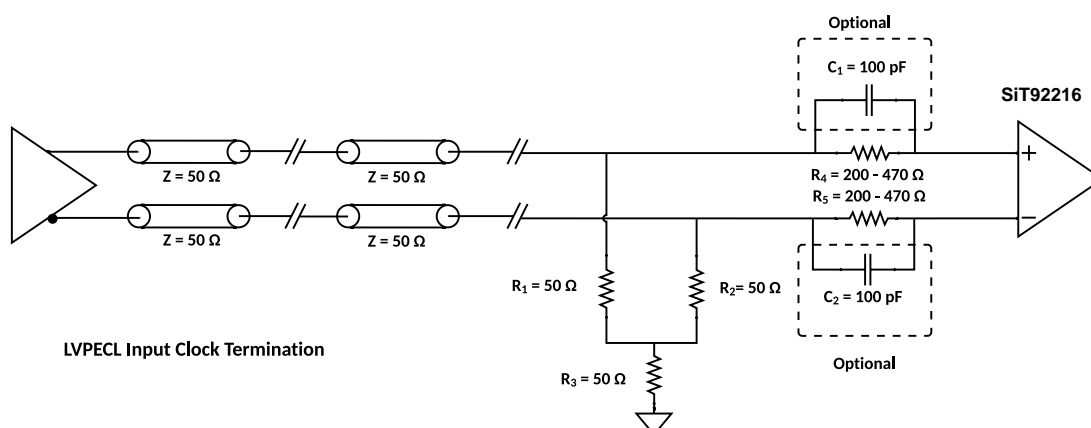
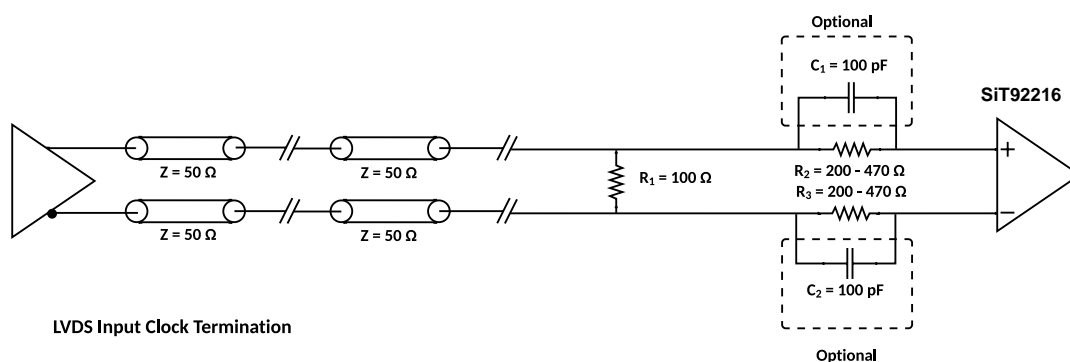
For example, [Figure 37](#) shows a typical LVPECL driver and differential input. If the power of the driver ( $V_{CCO}$ ) is turned on before the input supply ( $V_{CCI}$ ), there is a possibility that the input current could exceed the limit and damage diode D1.

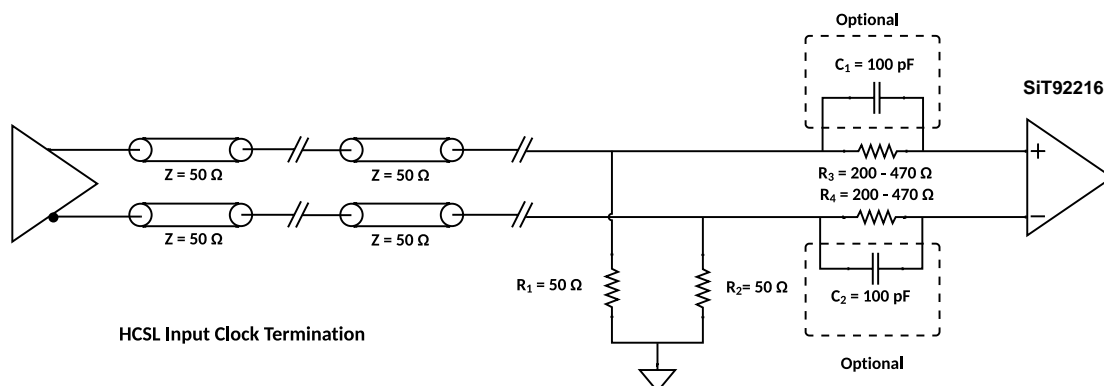


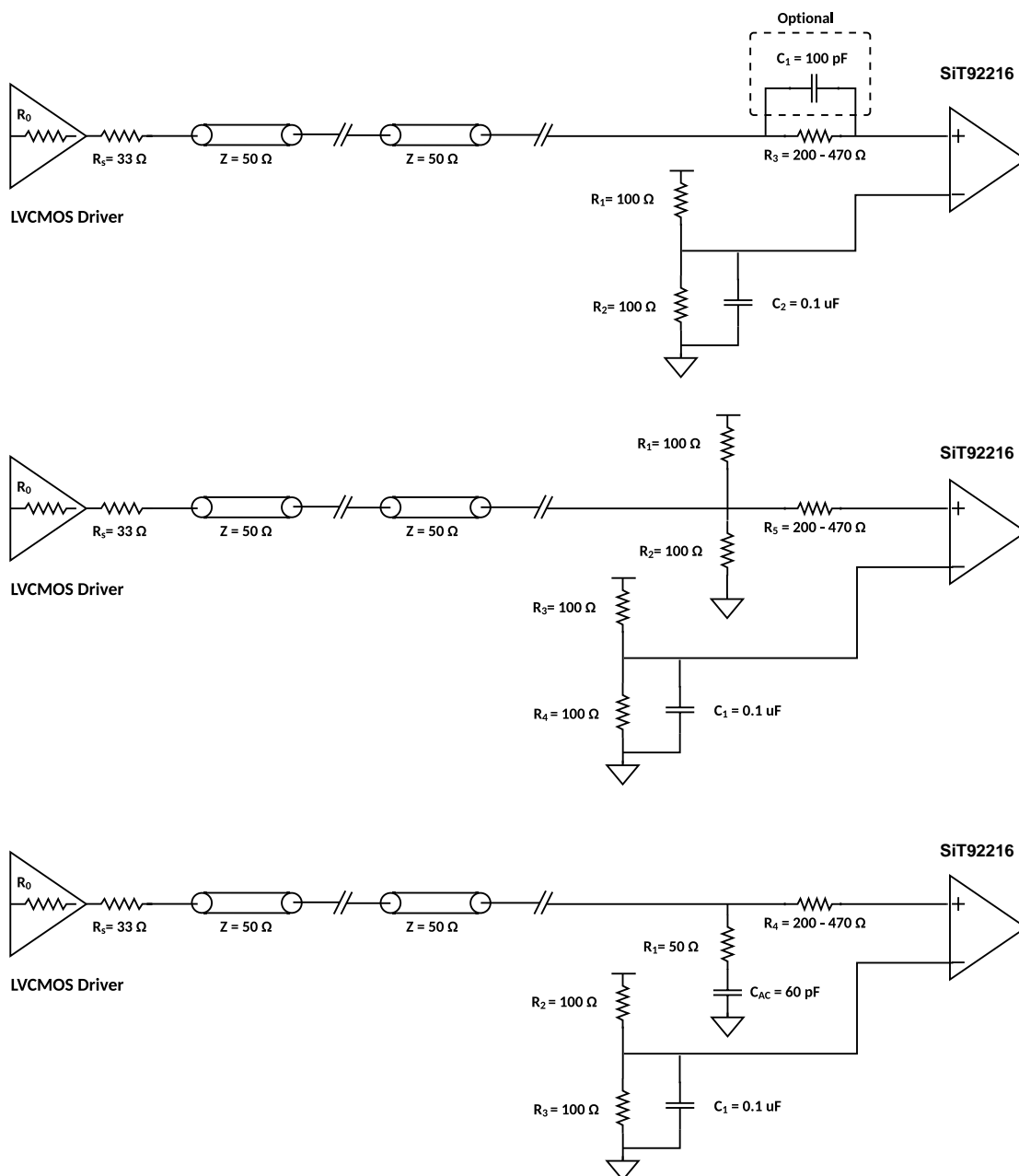
**Figure 37. Typical input differential clock**

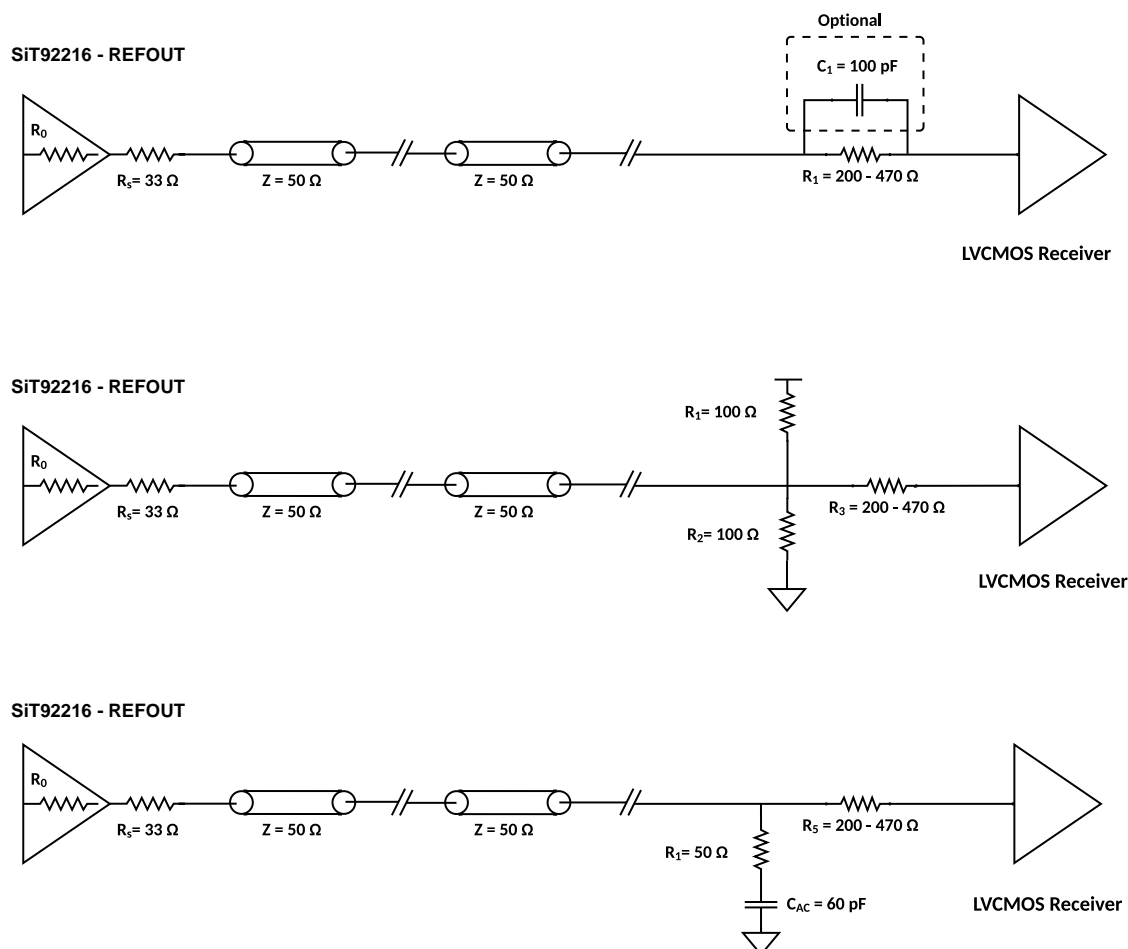
To ensure the input current does not exceed its limit and damage the device, a current limiting resistor can be used. Below are examples of the most common termination topologies using a series current limiting resistor. Though it's not necessary, but if board space allows, some of the

examples have an optional 100pf capacitor which assists with the integrity of the rise time. It is also recommended that the current limiting resistor be as close to the receiver as possible.

**Input Clock Termination with Hot Swap Protection****LVPECL Termination Example****Figure 38. LVPECL termination with hot swap protection****Figure 39. LVEPCL termination with hot swap protection****LVDS Input Clock Termination Example****Figure 40. LVDS termination with hot swap protection**

**HCSL Input Clock Termination Example****Figure 41. HCSL termination with hot swap protection**

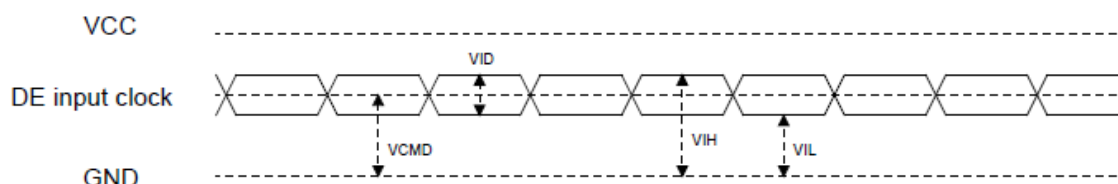
**LVCMOS Input Clock Termination with Hot Swap Protection****Figure 42. LVCMOS input clock termination with hot swap protection**

**LVCMOS Output Clock Termination with Hot Swap Protection****Figure 43. Different types of LVCMOS output clock termination with hot swap protection**

## Parameter Measurement Information

### Differential Input Level

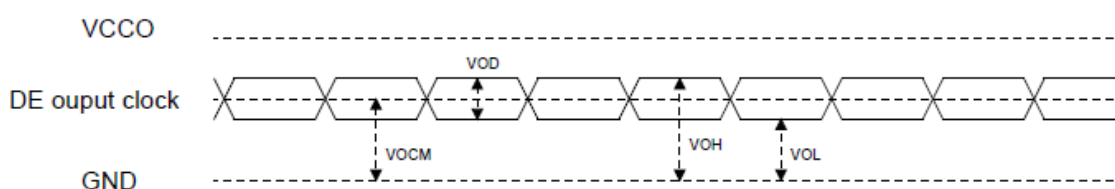
The parameter definitions related to differential input level is shown in [Figure 44](#).



**Figure 44. Parameters related to differential input level**

### Differential Output Level

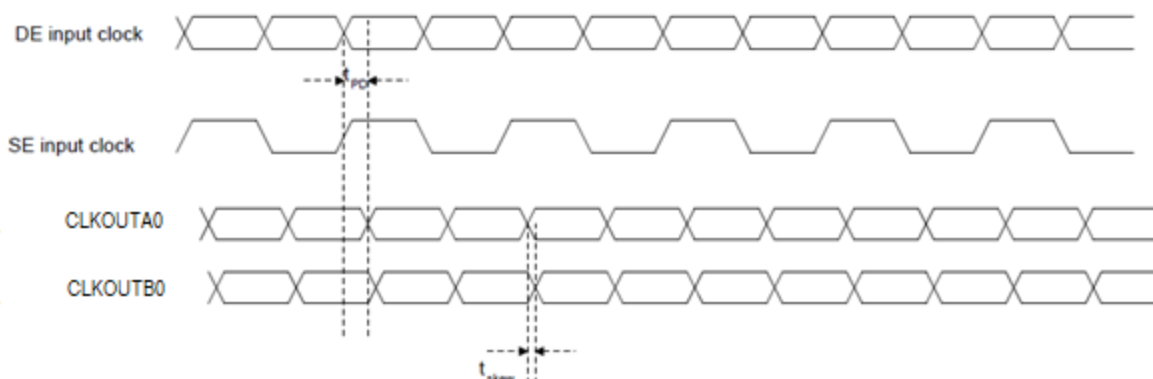
The parameter definitions related to differential output level is shown in [Figure 45](#)



**Figure 45. Parameters related to differential output clock levels**

### Skew and Input to Output Delay

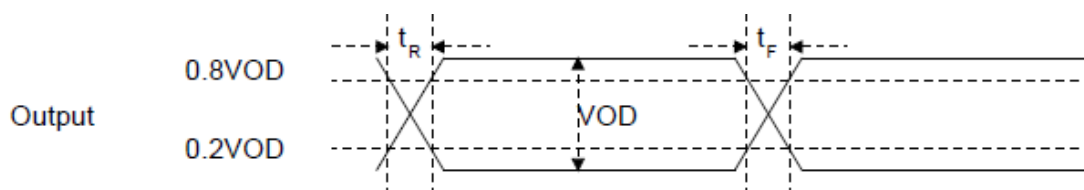
The parameter definitions related to propagation delay and skew are shown in [Figure 46](#)



**Figure 46. Parameter definitions of propagation delay and skew**

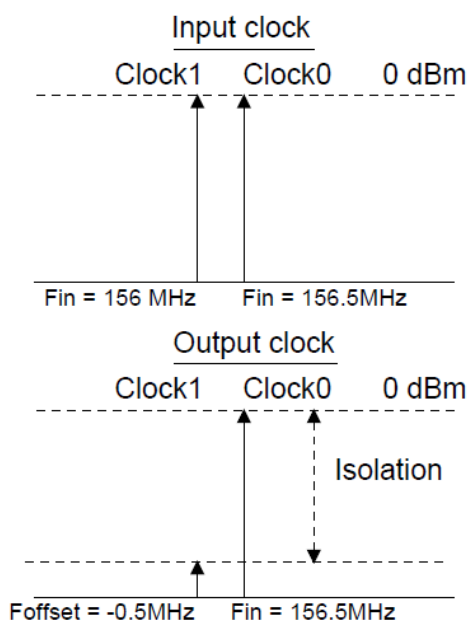
### Rise and Fall Times

The parameter definitions related to propagation rise and fall times are shown in [Figure 47](#).

**Figure 47. Parameter definitions related to rise and fall times****Isolation**

Isolation is a measure of the coupling of clock toggling in unselected input clock path on the output clock. Let us say that CLOCK0 path is selected and there the clock frequency

is 156.5 MHz at 0 dBm power. If a clock is toggling in CLOCK1 path at 156 MHz at 0 dBm, then there may be a tone at an offset of 0.5 MHz from the carrier, in the output clock. The power of this tone with respect to the carrier is called isolation.

**Figure 48. Parameter definition of isolation****Operation in Multiple VCCO Supply Domains**

The VCCOA pins, 2 and 5 on the left side are shorted internally. These pins along with ODR CLKOUTA0 to CLKOUTA1 belong to a single supply domain. The VCCOB pins, 20 and 23 on the right side are shorted internally. These pins along with ODR CLKOUTB0 to CLKOUTB1 belong

to a single supply domain. These two supply domains are totally independent of each other. Pin 2 and 5 can be connected to say 3.3 V while pin 20 and 23 can be connected to 2.5 V. In this example, CLKOUTA0 to CLKOUTA1 will be 3.3 V output driver. CLKOUTB0 to CLKOUTB1 will be 2.5 V output driver.

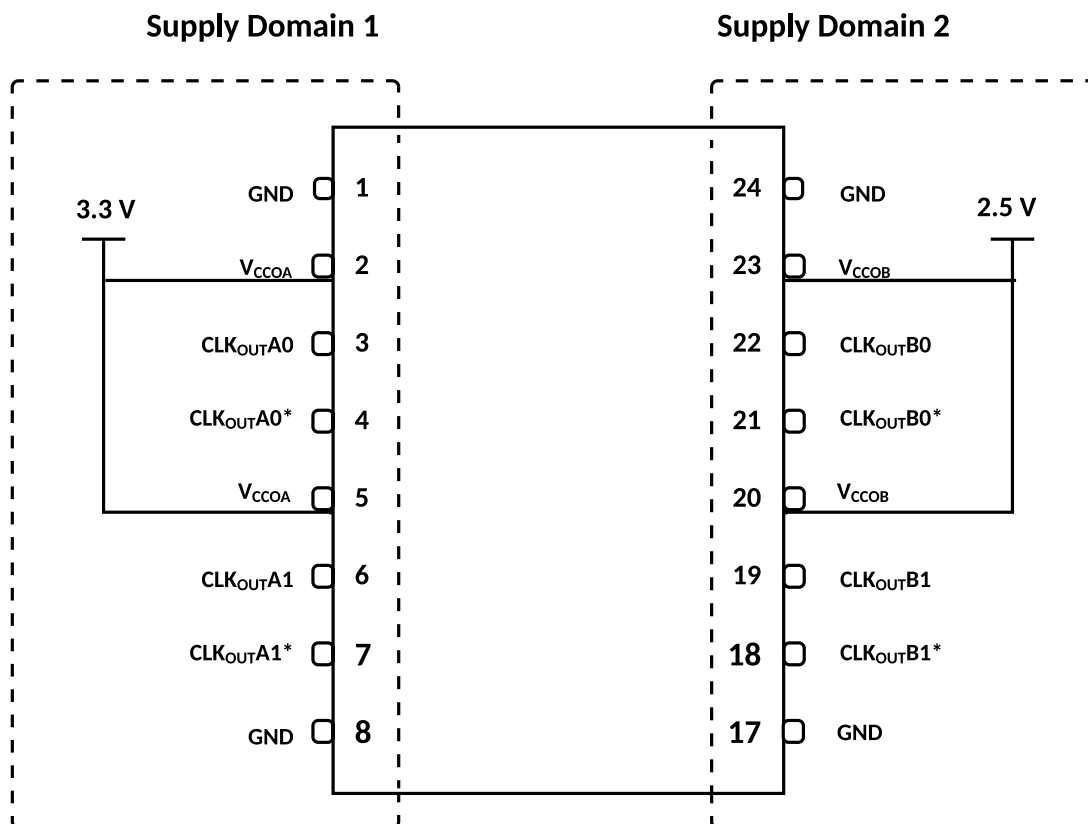
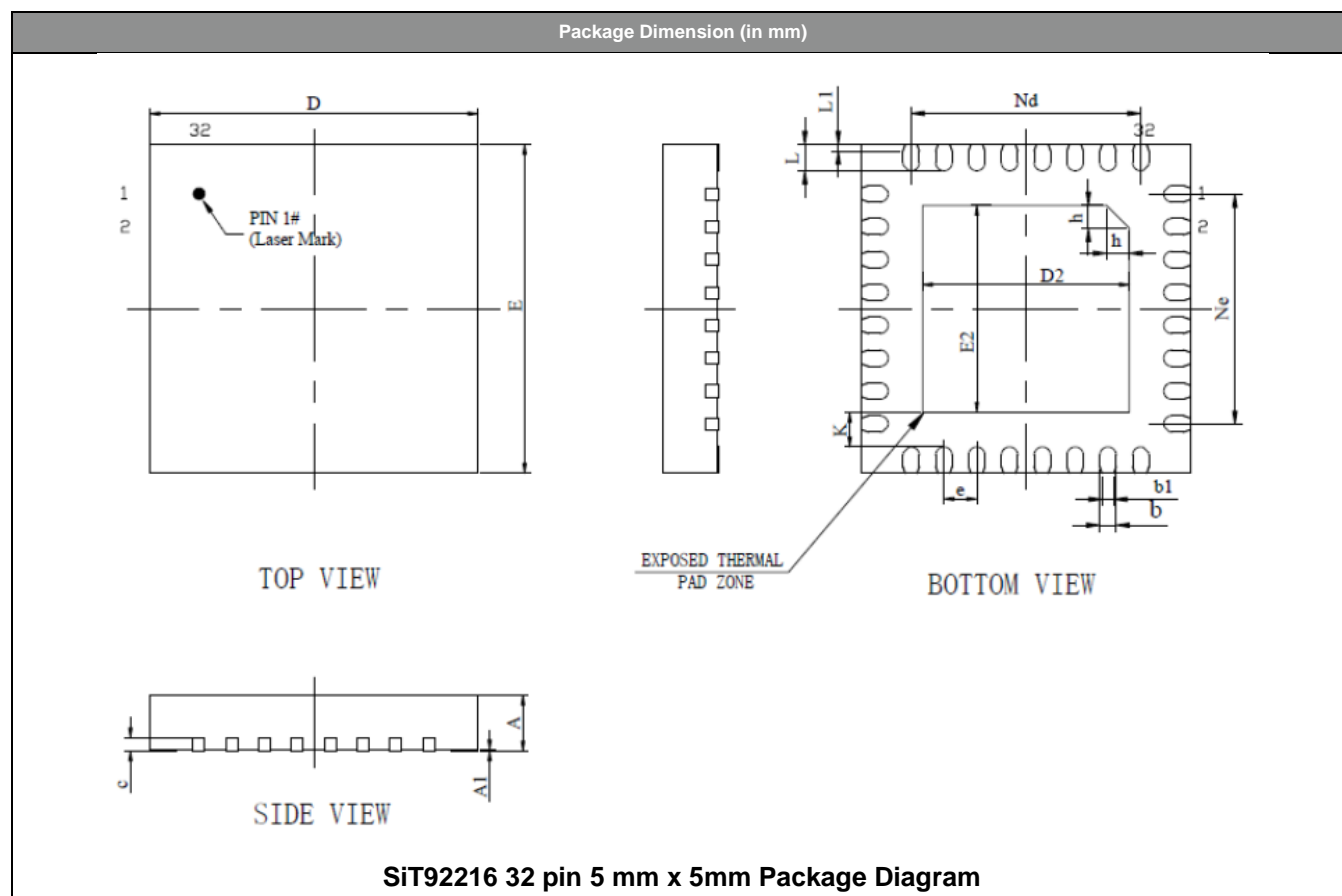
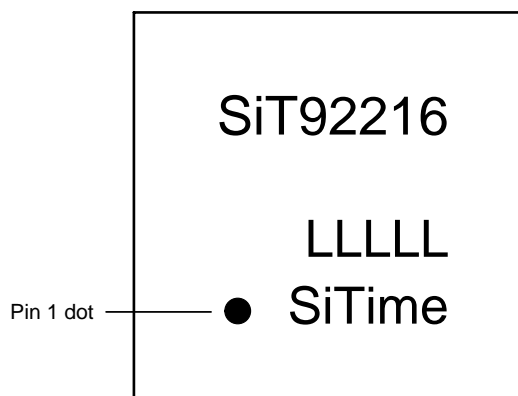


Figure 49. Multi Supply operation of SiT92216

**Package Dimensions and patterns****Notes:**

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0	0.02	0.05
b	0.20	0.25	0.30
b1	0.18 REF		
c	0.203 REF		
D	4.90	5.00	5.10
D2	3.05	3.15	3.25
e	0.50 BSC		
Nd	3.50 BSC		
Ne	3.50 BSC		
E	4.90	5.00	5.10
E2	3.05	3.15	3.25
L	0.35	0.40	0.45
L1	0.10 REF		
h	0.30	0.35	0.40
K	0.525 REF		

**Top Marking**

Line 1: "SiT92216", SiTime part number

Line 2: Blank

Line 3: "LLLLL", Lot code from SiTime

Line 4: Pin 1 dot and "SiTime" logo

## Revision History

**Table 23. Revision History**

Revisions	Release Date	Change Summary
0.5	10-Nov-2023	Initial Release
0.51	8-Jul-2024	Ordering Information update
0.52	31-Jan-2025	Ordering Code for Packaging updated with 4Ku/reel code "P" Added Top Marking section

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